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(FILE 'HOME' ENTERED AT 14:49:40 ON 07 JAN 2002)

FILE 'REGISTRY' ENTERED AT 14:50:03 ON 07 JAN 2002

L1 476 S (SI AND O)/ELS AND 2/ELC.SUB
 L2 425 S (SI AND N)/ELS AND 2/ELC.SUB
 L3 318 S (SI AND O AND N)/ELS AND 3/ELC.SUB
 E ALUMINUM/CN
 E TUNGSTEN/CN
 L4 1 S E3
 E COPPER/CN
 L5 1 S E3
 E CHROMIUM/CN
 L6 1 S E3
 E GOLD/CN
 L7 1 S E3
 E PLATINUM/CN
 L8 1 S E3
 E PALLADIUM/CN
 L9 1 S E3
 E GERMANIUM/CN
 L10 1 S E3
 E SELENIUM/CN
 L11 1 S E3

FILE 'HCAPLUS' ENTERED AT 14:59:17 ON 07 JAN 2002

 E POLYIMIDE/CT
 E E3+ALL/CT

L23 1470020 S (ALUMINUM OR AL OR TUNGSTEN OR W)
 L24 1274581 S (COPPER OR CU OR CHROMIUM OR CR OR GOLD OR AU)
 L25 399796 S (PLATINUM OR PT OR PALLADIUM OR PD)
 L26 258610 S (SELENIUM OR SE OR GERMANIUM OR GE)
 L27 36496 S SILICON(W)OXIDE OR SI(W)OXIDE OR SIO OR (OXOSILYLENE(W)28SI)
 L28 67146 S SILICON(W)NITRIDE OR SI(W)NITRIDE OR SIN OR (SILICON(2N) MONO
 L29 7537 S ((SILICON (N)NITRIDE(N) OXIDE) OR (SILICON (N)NITRIDE(N) OXID
 L30 55621 S DIAMOND OR (DIAMOND(3N)CARBON)
 L31 1376 S ((FLUORIN?)(W) (DOP?)(W) (OXIDE?) OR (F)(W)(DOP?) OR (FLUORIN
 L32 594 S ANTI(W)FUSE# OR ANTIFUSE# OR OTP OR ((ONE)(N)(TIME)(N)(PROGRA
 L33 304000 S (DIELECTRIC? OR OXIDE OR INSULAT?)(3N)(FILM# OR LAYER? OR COA
 L34 2663193 S (ANTI(N)REFLECT? OR (COAT#### OR FILM# OR LAYER?)) OR ((DICHRO

FILE 'REGISTRY' ENTERED AT 15:08:11 ON 07 JAN 2002

 E DIAMOND/CN

L35 1 S E3

FILE 'HCAPLUS' ENTERED AT 15:08:30 ON 07 JAN 2002

L36 31653 S L35
 E COMPOUND SEMICONDUCTOR/CT
 E E4
 E E3+ALL/CT

L37 1119 S E2

FILE 'REGISTRY' ENTERED AT 15:15:35 ON 07 JAN 2002

FILE 'REGISTRY' ENTERED AT 15:17:27 ON 07 JAN 2002

L38 256169 S PACR/PCT
 L39 251968 S L38 AND POLY?

01/07/2002

Serial No.:09/873,537

L40 30979 S L39 AND METHACRYLATE?
L41 31175 S L38 AND METHACRYLATE?
L42 31175 S L40 OR L41

FILE 'HCAPLUS' ENTERED AT 15:19:41 ON 07 JAN 2002
L43 139520 S L42
L44 2368 S POLYMETHYLMETHACRYLATE

FILE 'REGISTRY' ENTERED AT 15:28:46 ON 07 JAN 2002
L45 45348 S PI/PCT
L46 73701 S PA/PCT
E PARALYENE
E PARALYENE/CN

FILE 'HCAPLUS' ENTERED AT 15:29:52 ON 07 JAN 2002
L47 28418 S L45
L48 158 S L32 AND L33

FILE 'REGISTRY' ENTERED AT 15:53:22 ON 07 JAN 2002
E DIAMOND/CN
L49 1 S E3

FILE 'HCAPLUS' ENTERED AT 15:53:42 ON 07 JAN 2002
L50 38 S L48 AND (VIA OR VIAS)
L51 14 S L50 AND (L49 OR L1 OR L2 OR L27 OR L28 OR L30 OR L31)
L52 64 S L48 AND (L49 OR L1 OR L2 OR L27 OR L28 OR L30 OR L31)
L53 54 S L48 AND (TRENCH? OR HOLE? OR GROOVE# OR CHANNEL OR EDGE? OR F
L54 23 S L53 AND (L49 OR L1 OR L2 OR L27 OR L28 OR L30 OR L31)
L55 1 S L48 AND (L45 OR POLYIMIDE? OR L46 OR POLYAMIDE? OR PARALYENE)
L56 0 S L48 AND L44
L57 73 S L50 OR L53
L58 45 S L57 AND (L1-L8 OR L23 OR L24 OR L25 OR GOLD OR AU)
L59 73 S L57 AND (L1 OR L2 OR L27 OR L28 OR (AMORPHOUS(N)(SI OR SILICO
L60 22 S (L52 AND L59 AND L54 AND L58)
L61 30 S L51 OR L54
L62 30 DUP REMOVE L61 (0 DUPLICATES REMOVED)
L63 0 S L60 NOT L61
L64 30 S L61 OR L60
L65 30 S L51 OR L64
S L48 AND (PARALYENE/CN)

FILE 'REGISTRY' ENTERED AT 17:11:14 ON 07 JAN 2002
L66 0 S PARALYENE/CN

FILE 'HCAPLUS' ENTERED AT 17:11:16 ON 07 JAN 2002
L67 0 S L66
L68 0 S L48 AND (L67)

FILE 'REGISTRY' ENTERED AT 17:11:43 ON 07 JAN 2002
L69 0 S PARALYENE

FILE 'HCAPLUS' ENTERED AT 17:12:50 ON 07 JAN 2002
L70 1 S PARALYENE
L71 808 S PARYLENE

FILE 'REGISTRY' ENTERED AT 17:17:15 ON 07 JAN 2002
L72 1 S PARYLENE/CN

FILE 'HCAPLUS' ENTERED AT 17:17:34 ON 07 JAN 2002

01/07/2002

Serial No.: 09/873,537

=> S L48 AND(L72 OR L71)
1051 L72
L73 0 L48 AND(L72 OR L71)

L64 ANSWER 1 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 2001:868915 HCAPLUS
 DN 136:14099
 TI One time programmable read only memory
 IN Chang, Kuang-yeh
 PA Taiwan
 SO U.S. Pat. Appl. Publ., 9 pp.
 CODEN: USXXCO
 DT Patent
 LA English
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2001045594	A1	20011129	US 1999-239033	19990127
AB	Provided is a 1 time programmable read only memory, which includes a floating gate, an inter-metal dielec. layer and a control gate stacked on each other on a substrate. Also, ion-implanted regions are formed in the substrate on both sides of the stacked gate structure, and are covered by metal silicide layers. The inter-metal dielec. layer comprises an oxide layer and a Si nitride layer, in which the oxide layer covers the floating gate, and the Si nitride layer further covers the floating gate and the metal silicide layer. The control gate covers the Si nitride layer. Also, the 1 time programmable read only memory of the invention not only can reduce the elec. resistance of bit lines and enhance its own performance, but also has a small size and a greater planarity due to an absence of field oxide layers and contact windows formed thereon and therein.				

L64 ANSWER 2 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 2001:691691 HCAPLUS
 DN 135:234905
 TI Procedure for manufacturing a wiring plane on a semiconductor chip with an antifuse.
 IN Lehr, Matthias; Leiberg, Wolfgang
 PA Infineon Technologies A.-G., Germany
 SO Ger., 8 pp.
 CODEN: GWXXAW
 DT Patent
 LA German
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	DE 10021098	C1	20010920	DE 2000-10021098	20000420
	EP 1148542	A2	20011024	EP 2001-107218	20010323
	R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO				

PRAI DE 2000-10021098 A 20000420
 AB According to the invention a buried anti-reflection layer is used in a dielec. layer with the prodn. of a wiring plane on a semiconductor chip with antifuses, in which via holes are formed which are used for optical lithog. to form line drains over the via holes by using one-step etching only.

RE.CNT 5

L64 ANSWER 3 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 2001:537446 HCAPLUS
 DN 135:101076

TI Method of making a barrier **layer** to protect programmable antifuse structure from damage during fabrication sequence

IN Hsu, Woan Jen; Liu, Chi Kang
 PA Taiwan Semiconductor Manufacturing Company, Taiwan
 SO U.S., 11 pp.

CODEN: USXXAM
 DT Patent
 LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI US 6265257 B1 20010724 US 1999-409877 19991001

AB A method for forming an **antifuse** interconnect structure, for a 1-time fusible link, to be used with field-programmable gate arrays, has been developed. The process features the use of an **amorphous Si layer**, used as the **antifuse layer**, with the **amorphous Si layer** protected by a thin barrier layer, during the patterning procedure. The protected **antifuse layer** results in a reproducible thickness, and thus reproducible pulsing voltages, needed for rupturing of the **antifuse layer**. Planarization of an underlying metal plug, via a conductor **layer** refill procedure, offers a smooth top surface, **flush** with the top surface of the adjacent interlevel **dielec. layer**, for the overlying **antifuse layer**.

L64 ANSWER 4 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 2001:464313 HCAPLUS
 DN 135:39751

TI Method of making a dual damascene **anti-fuse** prior to via fabrication without using dedicated lithographic masking levels

IN Radens, Carl J.; Brintzinger, Axel C.
 PA International Business Machines Corporation, USA; Infineon Technologies North America Corp.

SO U.S., 9 pp.
 CODEN: USXXAM

DT Patent
 LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI US 6251710 B1 20010626 US 2000-560072 20000427
 JP 2001358224 A2 20011226 JP 2001-133328 20010427

US 2001036750 A1 20011101 US 2001-873537 20010604

PRAI US 2000-560072 A 20000427

AB An interconnect structure in which a patterned **antifuse** material is formed therein comprising: a substrate having a 1st level of elec. conductive features; a patterned **anti-fuse** material, formed on said substrate, wherein said patterned **anti-fuse** material includes an opening to at least one of said 1st level of elec. conductive features; a patterned interlevel **dielec** material formed on said patterned **anti-fuse** material, wherein said patterned interlevel **dielec** includes **vias**, as least one of said **vias** includes a **via** space; and a 2nd level of elec. conductive features formed in said **vias** and

via spaces.

L64 ANSWER 5 OF 30 HCPLUS COPYRIGHT 2002 ACS
AN 2001:449934 HCPLUS
DN 135:39676
TI Design and fabrication of a dielectric-based anti-fuse
cell with a polysilicon contact plug
IN Bergemont, Albert; Kalnitsky, Alexander
PA National Semiconductor Corporation, USA
SO U.S., 11 pp.
CODEN: USXXAM
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE	
	-----	-----	-----	-----	-----	
PI	US 6249010	B1	20010619	US 1998-135536	19980817	
AB	A dielec.-based anti-fuse cell and cell array, that include a doped polysilicon contact plug, with a low resistance in the programmed state, a low capacitance, and a small cell area. The dielec.-based anti-fuse cell includes a 1st insulating layer, typically SiO ₂ , on the surface of a semiconductor substrate. A 1st doped polysilicon (poly 1) layer is on the upper surface of the 1st insulating layer and a 2nd insulating layer is over the poly 1 layer. A doped polysilicon contact plug extends through the 2nd insulating layer and into the poly 1 layer. A dielec. layer, typically either an ONO or NO dielec. composite layer, covers the upper surface of the doped polysilicon contact plug. A 2nd doped polysilicon (poly 2) layer is disposed on the dielec. layer. A process for manufg. the anti-fuse cell and array includes 1st providing a semiconductor substrate and forming a 1st insulating layer on its surface. Next a poly 1 layer (e.g. bit lines) is formed on the surface of the 1st insulating layer followed by the formation of a 2nd insulating layer over the poly 1 layer. A contact opening that extends into the poly 1 layer is then created in the 2nd insulating layer and filled with a doped polysilicon contact plug. Next, a dielec. layer is formed on the upper surface of the doped polysilicon contact plug, followed by the formation of a poly 2 layer (e.g. word lines) on the upper surface of the dielec. layer					

L64 ANSWER 6 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 1999:90366 HCAPLUS
 DN 130:132793
 TI Double half **via** antifuse fabricated with low sensitivity to selective etching during **via** formation
 IN McCollum, John L.
 PA Actel Corporation, USA
 SO U.S., 7 pp., Cont.-in-part of U.S. 5,552,627.
 CODEN: USXXAM
 DT Patent
 LA English
 FAN.CNT 6

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 5866937	A	19990202	US 1995-482270	19950607
	US 5070384	A	19911203	US 1990-508306	19900412
	US 5181096	A	19930119	US 1990-604779	19901026
	JP 04226068	A2	19920814	JP 1991-171589	19910412
	JP 3095811	B2	20001010		
	JP 04282864	A2	19921007	JP 1991-305470	19911024
	US 5411917	A	19950502	US 1993-4912	19930119

B An antifuse comprises a substantially planar conductive lower electrode covered by a 1st layer of **Si nitride**. A layer of **amorphous Si** is disposed over the **Si nitride layer**. A 1st dielec. layer is disposed over the surface of the **amorphous Si** layer and has a 1st aperture there through communicating with the **amorphous Si** layer. A 2nd layer of **Si nitride** is disposed over the 1st dielec. layer and in the 1st aperture. A conductive upper electrode, such as a layer of **Ti nitride**, is disposed over the 2nd layer of **Si nitride**. A 2nd dielec. layer is disposed over the surface of the conductive upper electrode and has a 2nd aperture there through in alignment with the 1st aperture communicating with the conductive upper electrode. An overlying metal layer is disposed over the surface of the 2nd dielec. layer and in the 2nd aperture making elec. contact with the conductive upper electrode.

RE.CNT 5

L64 ANSWER 7 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 1999:77382 HCAPLUS
 DN 130:132765
 TI Semiconductor nonvolatile memory device and manufacture thereof
 IN Araki, Hitoshi; Hatakeyama, Masao
 PA Toshiba Corp., Japan
 SO Jpn. Kokai Tokkyo Koho, 15 pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 11026620	A2	19990129	JP 1998-75343	19980324
PRAI	JP 1997-116753		19970507		

AB The invention relates to a semiconductor nonvolatile memory cell, e.g., a PROM, an OTP (one time PROM), an EEPROM, a flash EEPROM, wherein the degrdn. of tunnel oxide film at the trench

corner or the LOCOS edge is minimized.

L64 ANSWER 8 OF 30 HCPLUS COPYRIGHT 2002 ACS

AN 1999:34438 HCPLUS

DN 130:89329

TI Fabricating an amorphous silicon **antifuse** structure

IN Love, Michela S.; Parks, Delbert H.

PA VLSI Technology, Inc., USA

SO U.S., 6 pp.

CODEN: USXXAM

DT Patent

LA English

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI US 5856213	A	19990105	US 1996-687234	19960725
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AB An **antifuse** structure is formed between 2 metal contacts in which a thin **oxide** layer is formed on the 1st or bottom metal, a shallow **via** is provided in the **oxide** layer, and a **layer** of amorphous Si is deposited over the thin oxide and into the shallow **via** without leaving the usual furrows in the amorphous Si, thereby eliminating the step coverage problems of cusps forming in the subsequently applied 2nd or top metal.

L64 ANSWER 9 OF 30 HCPLUS COPYRIGHT 2002 ACS

AN 1998:550586 HCPLUS

DN 129:169222

TI **Antifuse**-programmed PROM cell

IN McCollum, John

PA Actel Corporation, USA

SO PCT Int. Appl., 17 pp.

CODEN: PIXXD2

DT Patent

LA English

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI WO 9835387	A1	19980813	WO 1998-US2924	19980210
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W: JP, KR

RW: AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE

US 5909049	A	19990601	US 1997-797202	19970211
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EP 976158	A1	20000202	EP 1998-905091	19980210
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R: DE, FR, GB, IT

PRAI US 1997-797202 19970211

WO 1998-US2924		19980210
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AB An **antifuse**-based PROM cell design allows large currents to be sunked during cell programming to ensure low programmed resistance of the cell while using min.-geometry select devices. This is achieved by using a pseudo-SCR latchup effect during programming. The regions in the semiconductor substrate forming lower **antifuse** electrodes for the **antifuses** in the PROM cells are doped at low levels with P. An **antifuse** layer formed from an **oxide**,

oxide-nitride, or **oxide-nitride-oxide antifuse**

layer is formed over the lower **antifuse** electrode, and

an upper **antifuse** electrode is formed from polysilicon. A

min.-geometry N-channel select transistor is formed in series

with the **antifuse** to complete the PROM cell. The drain and

source diffusions of the select transistor are As-doped and the drain

diffusion is contiguous with the lower **antifuse** electrode. A

bit line is contacted to the upper **antifuse** electrode and the select transistor gate is part of a polysilicon word line. The source diffusion of the select transistor is grounded.

L64 ANSWER 10 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 1998:199628 HCAPLUS
 DN 128:264874
 TI Semiconductor devices having an **antifuse** built in an integrated circuit for field programmable gate arrays
 IN Sakurai, Koji; Yuasa, Hiroshi; Yamaoka, Toru; Honta, Koji
 PA Matsushita Electronics Corp., Japan
 SO Jpn. Kokai Tokkyo Koho, 11 pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 10084043	A2	19980331	JP 1996-237474	19960909

AB The title devices comprise a 1st interlayer **insulator** film formed on a semiconductor substrate, a contact **hole** provided through the 1st interlayer **insulator** film and reached to the substrate, a 1st metallic circuit **layer** connected to the substrate through the contact **hole**, a 2nd interlayer **insulator** film covering over the 1st circuit **layer** and on the 1st interlayer **insulator** film, a 2nd metallic circuit formed on the 2nd interlayer **insulator** film, an **antifuse** film formed on the 2nd metallic circuit **layer**, and a 3rd metallic circuit **layer** formed on the **antifuse**. The **antifuse** film bound between the 2nd and 3rd metallic circuit **layers** are leveled so as to give precision controlled **antifuse** characteristics such as insulative breakdown voltage.

L64 ANSWER 11 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 1998:180602 HCAPLUS
 DN 128:224871
 TI **Antifuses** and stacked capacitors in integrated circuits and blowing of the **antifuses**
 IN Dennison, Charles H.
 PA Micron Technology, Inc., USA
 SO U.S., 12 pp.
 CODEN: USXXAM
 DT Patent
 LA English
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 5726483	A	19980310	US 1995-503022	19950717
US 5756393	A	19980526	US 1997-822991	19970321
US 6146925	A	20001114	US 1998-14766	19980128
US 6221729	B1	20010424	US 1998-83624	19980522
US 6291871	B1	20010918	US 1999-244557	19990203

PRAI US 1995-503022 A3 19950717
 US 1997-822991 A1 19970321
 US 1998-14766 A3 19980128

AB A method of jointly forming stacked capacitors and **antifuses** includes (a) providing a common **layer** of elec. conductive material to form both a capacitor storage node and an inner

antifuse plate; (b) providing a common layer of dielec. material over the capacitor storage node and the inner antifuse plate, the common layer of dielec. material comprising both an intervening capacitor dielec. element and an intervening antifuse dielec. element, the common layer of dielec. material having a 1st breakdown voltage per unit length for a given current per unit area; (c) providing a common layer of elec. conductive material over the common layer of dielec. material to form both a capacitor cell layer and an outer antifuse plate; (d) providing a lateral edge of the outer antifuse plate and a lateral edge of the intervening antifuse dielec. element; and (e) depositing an antifuse breakdown layer of dielec. material over the lateral edges of the outer antifuse plate and the intervening antifuse dielec. element, the antifuse breakdown layer having a 2nd breakdown voltage per unit length for the same given current per unit area, which is lower than the 1st breakdown voltage per unit length. Novel antifuse constructions, integrated circuits, and blowing of antifuses are also disclosed.

L64 ANSWER 12 OF 30 HCPLUS COPYRIGHT 2002 ACS
AN 1997:180640 HCPLUS

DN 126:180005

TI Semiconductor device containing antifuses with good flatness and its manufacture

IN Yamazaki, Satoshi

PA Yamagata Nippon Denki Kk, Japan

SO Jpn. Kokai Tokkyo Koho, 5 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 08330530	A2	19961213	JP 1995-133672	19950531
	JP 2648134	B2	19970827		

AB The device includes an antifuse element contg. a contact hole in a laminate of: a 1st insulating film, an interlayer-insulating film contg. SiN and a 2nd insulating film, and a 1st Al-based wiring pattern, where a 2nd Al-based wiring pattern is formed on the 1st wiring pattern at the hole bottom via a 3rd insulating film. The 2nd insulating film may be polyimide. The manufg. process, including dry-etching for the contact hole and temp.-controlled annealing for simultaneous formation of the 2nd and the 3rd insulating films, is also claimed. The manuf. shows good through put.

L64 ANSWER 13 OF 30 HCPLUS COPYRIGHT 2002 ACS

AN 1996:607555 HCPLUS

DN 125:236087

TI Antifuse with a double-via spacer-defined contact and its manufacture

IN Iranmanesh, Ali

PA Crosspoint Solutions, Inc., USA

SO PCT Int. Appl., 25 pp.

CODEN: PIXXD2

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 9625766	A1	19960822	WO 1996-US2024	19960209
	W: JP, KR				
	RW: AT, BE, CH, DE, DK, ES, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE				
	US 5663591	A	19970902	US 1995-388673	19950214

PRAI US 1995-388673 19950214

AB The present invention provides for a method of forming an **antifuse** in an integrated circuit having a **1st insulating layer** on a semiconductor substrate. The method comprises forming a **1st metal interconnection layer** on the **1st insulating layer**; forming a relatively thin, **2nd insulating layer** over the **1st metal interconnection layer** with a **via** where the **antifuse** is to be located to expose the **1st metal interconnection layer**; forming **1st spacer regions** on the sidewalls of the **2nd insulating layer**; forming a **programming layer** on the **2nd insulating layer** and in the **via** to contact the **1st metal interconnection line**; forming **2nd spacer regions** on the sidewalls of the **programming layer** in the **via**; forming a **barrier metal layer** on the **programming layer**; forming a relatively thick, **3rd insulating layer** on the **barrier metal layer** with a **2nd aperture** to expose a portion of the **barrier metal layer**; and forming a **2nd metal interconnection layer** on the **3rd insulating layer** and in the **2nd aperture** to contact the portion of the **barrier metal layer**.

L64 ANSWER 14 OF 30 HCPLUS COPYRIGHT 2002 ACS

AN 1996:563667 HCPLUS

DN 125:263124

TI Electrically programmable **antifuse** incorporating dielectric and amorphous silicon interlayers

IN McCollum, John L.; Eltoukhy, Abdelshafy A.; Forouhi, Abdul R.

PA Actel Corporation, USA

SO U.S., 15 pp. Cont.-in-part of U. S. 5,411,917.

CODEN: USXXAM

DT Patent

LA English

FAN.CNT 6

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 5552627	A	19960903	US 1994-231634	19940422
	US 5070384	A	19911203	US 1990-508306	19900412
	US 5181096	A	19930119	US 1990-604779	19901026

B An **antifuse** may be fabricated as a part of an integrated circuit in a **layer** located above and **insulated** from the **semiconductor substrate**. The **antifuse** includes a **lower 1st metal electrode**, a **1st antifuse dielec. layer** (preferably **Si nitride**) on the **lower 1st electrode**, and an **antifuse layer** (preferably amorphous Si) on the **1st dielec. layer**. An **interlayer dielec.** layer is disposed on the **antifuse layer** and includes an **antifuse via** formed completely through it. A **2nd antifuse dielec. layer** (preferably **Si nitride**) is disposed over the **amorphous Si layer** in the **antifuse via**, and an **upper 2nd metal electrode** is disposed over the **2nd dielec. layer** in the

antifuse via.

L64 ANSWER 15 OF 30 HCPLUS COPYRIGHT 2002 ACS
 AN 1996:551149 HCPLUS
 DN 125:210272
 TI Antifuse semiconductor integrated circuits
 IN Jinriki, Hiroshi; Tamura, Yoshimitsu; Kimura, Yoshitaka; Tsutsui, Chie;
 Oota, Tomohiro; Komya, Takayuki
 PA Kawasaki Steel Corp., Japan
 SO Jpn. Kokai Tokkyo Koho, 38 pp.
 CODEN: JKXXAF

DT Patent
 LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 08153799	A2	19960611	JP 1995-210670	19950818
	JP 3104843	B2	20001030		
	US 5565702	A	19961015	US 1994-353296	19941205
	US 5641985	A	19970624	US 1994-353294	19941205
	US 5679974	A	19971021	US 1994-353287	19941205

AB The circuit has its lower **layer** electrodes made of an amorphous conductive material. The upper **layer** electrode may be made of an amorphous conductive material. The conductive material may be (1) a compd. from .apprx.>2 of Co, Ni, Cu, Ti, Zr, Nb, Mo, Hf, Ta, and W (group 1), (2) a compd. from .apprx.>1 of Group 1 with .apprx.>1 of Si, B, N, C, Ge, As, P, and Sb (Group 2), or Al, or Y and/or La, and Al, (3) Y-La or a compd. from Y and/or La with Al, or (4) a compd. from Au, Pt, Pd, and/or Ag with .apprx.>1 of Group 2, .apprx.>1 of Group 1, or Y and/or La. The lower **layer** electrode may be a metal silicide with compn. ratio of the metal higher than the stoichiometric ratio. The lower and the upper **layer** electrode may be formed from a material contg. refractory metal(s) and a low m.p. metal lower in resistivity than the refractory metal(s), resp. The circuit may have (1) the lower wiring **layer** consisting of an Al alloy film and the uppermost **layer** of TiN, the lower **layer** electrode from the Al alloy film with removal of the TiN film in the depth direction at the bottom of the contact hole, **antifuse insulating films** from a SiO₂, a Si₃N₄, or a Ta₂O₅ film, and the upper **layer** electrode with the lowermost **layer** from an Al alloy which forms a contact to **antifuse insulating film** of the upper wiring, or (2) the lower **layer** electrode forming a contact of the lower wiring from an Al or an Al alloy monolayer to the **antifuse insulating film**, the upper **layer** electrode from Al or an Al alloy, and the lower wiring located immediately above an **insulating film** on the substrate and elec. connected to the substrate in a contact hole through a barrier metal composite film.

L64 ANSWER 16 OF 30 HCPLUS COPYRIGHT 2002 ACS
 AN 1996:250927 HCPLUS
 DN 124:329458
 TI Extremely low ON-resistance metal-to-metal **antifuses** with Al-Cu/10 nm-thick p-SiNx/Al-Cu structure for next generation very high speed FPGAs (field programmable gate arrays)
 AU Tamura, Yoshimitsu; Kimura, Yoshitaka; Tsutsui, Chie; Shinriki, Hiroshi

CS Advanced Technology Research Section, Kawasaki Steel Corp., Chiba, 260, Japan
 SO Jpn. J. Appl. Phys., Part 1 (1996), 35(2B), 1049-53
 CODEN: JAPNDE; ISSN: 0021-4922
 DT Journal
 LA English
 AB The authors present a novel metal-to-metal **antifuse** structure consisting of a plasma enhanced CVD **Si nitride** (p-SiNx) **dielec. film** sandwiched between two Al layers. The leakage current in the off-state is markedly reduced by using Al film as the upper electrode instead of Ti or TiN (Ti nitride) film. A Al-Cu/10 nm-thick p-SiNx/Al-Cu structure **antifuse** provides sufficient long-term off-state reliability exceeding ten years at 3.6 V while keeping low breakdown voltage (10 V). An extremely low on-resistance of .apprx.3 .OMEGA. and a narrow distribution are also realized. A new **antifuse** structure (Al-Cu/p-SiNx/Al-Cu(100 nm)/Ti/TiN/Al-Cu) highly compatible with the conventional **via** formation process in double metal interconnect wiring is proposed. This type of **antifuse** structure is very promising for next-generation very high-speed FPGAs.

L64 ANSWER 17 OF 30 HCPLUS COPYRIGHT 2002 ACS
 AN 1996:248262 HCPLUS
 DN 124:304901
 TI Semiconductor integrated circuit having **antifuse** structure and its manufacture
 IN Tanizaki, Yasunobu; Kobayashi, Masashi; Sawase, Terumi
 PA Hitachi Ltd, Japan; Hitachi Micro System Kk
 SO Jpn. Kokai Tokkyo Koho, 13 pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI JP 08031944 A2 19960202 JP 1994-163504 19940715
 AB In the **antifuse** structure a bottom electrode is **coated** with a **dielec. film** **via** a contact **hole** of an **insulator** having a controlled film thickness for a thickness uniformity of the **dielec. film** in the contact **hole**. The sides of the contact **hole** may be tapered. Or the bottom electrode is directly **coated** with a **dielec. film**. The top and bottom electrode may comprise silicide-forming metal (e.g., Ti, W, Mo, Ta) or its alloy and the **dielec. film** may comprise **amorphous Si**, SiO₂, Si₃N₄, SiC or other Si compd monolayer or multilayer. The manuf. involves forming the contact **hole** by isotropic etching or directly laminating the **dielec. film** on the bottom electrode. The **antifuse** structure is useful for a FPGA (field programmable gate array).

L64 ANSWER 18 OF 30 HCPLUS COPYRIGHT 2002 ACS
 AN 1995:1002485 HCPLUS
 DN 124:72867
 TI Interfacial reaction in the sputter-deposited SiO₂/TiO_{1.1}W_{0.9} **antifuse** system
 AU Baek, Jong Tae; Park, Hyung-Ho; Cho, Kyung-Ik; Yoo, Hyung Joun; Kang, Sang Won; Ahn, Byung Tae

CS Semiconductor Technol. Div., Electr. Telecommunications Res. Inst.,
 Taejon, 305-600, S. Korea
 SO J. Appl. Phys. (1995), 78(12), 7074-9
 CODEN: JAPIAU; ISSN: 0021-8979
 DT Journal
 LA English
 AB The effects of annealing temp. on the interfacial reactions and the **antifuse** I-V characteristics of ultra thin SiO₂ **layer** deposited on Ti_{0.1}W_{0.9} substrate were studied. The interfacial reactions were analyzed using XPS and Auger electron spectroscopy with the sample which is *in situ* annealed under ultra high vacuum or *ex situ* annealed in a nitrogen atm. The surface of the Ti_{0.1}W_{0.9} substrate was oxidized during sputter deposition of SiO₂ **layer**. Ti, W oxides consist of Ti₂O₃ (Ti₃O₅), TiO₂, WO₂, and WO₃. The WO₃ and Ti₂O₃ decompd. into metallic W and Ti at 400 and 500.degree., resp. The breakdown voltage of the **antifuse** decreased as the annealing temp. increased, due to the thinning of **dielec. layer** resulted from the decompn. of Ti, W oxides and the formation of metallic W and Ti. Annealing at 600.degree. caused the reaction between metallic (Ti,W) and SiO₂ **layer** and formed elemental silicon in the **dielec. layer**, where SiO₂ **layer** completely lost its **dielec.** property. The breakdown of **dielec.** property might from a metallic channel in the SiO₂ film, which mainly contains metallic W, Ti, and Si.

L64 ANSWER 19 OF 30 HCPLUS COPYRIGHT 2002 ACS
 AN 1995:982554 HCPLUS
 DN 124:19848
 TI Method of manufacturing an **antifuse** with silicon spacers and resulting **antifuse**
 IN Iranmanesh, Ali A.
 PA Crosspoint Solutions, Inc., USA
 SO PCT Int. Appl., 22 pp.
 CODEN: PIXXD2
 DT Patent
 LA English
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 9527313	A1	19951012	WO 1995-US3676	19950322
	W: JP, KR				
	RW: AT, BE, CH, DE, DK, ES, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE				
	US 5572062	A	19961105	US 1994-221344	19940331
PRAI	US 1994-221344		19940331		
AB	A method and resulting antifuse structure in an integrated circuit include a 1st metal interconnection layer on a 1st insulating layer over the substrate of the integrated circuit and a 2nd insulating layer over the metal interconnection layer . The 2nd insulating layer has a via therein and a programming layer located in the via . Such a programming layer includes a 1st region on the 1st metal interconnection layer which is removed from sides of the 2nd insulating layer in the via and a 2nd region on the sides of the 2nd insulating layer via . The 1st region has substantially a 1st thickness, and the 2nd region has substantially a 2nd thickness which is greater than the 1st thickness. Upon programming the antifuse structure, a conducting link forms in the 1st region of the programming layer .				

L64 ANSWER 20 OF 30 HCAPLUS COPYRIGHT 2002 ACS
AN 1995:503255 HCAPLUS
DN 122:304581
TI Manufacture of semiconductor devices
IN Tsuzuki, Norihisa
PA Fujitsu Ltd, Japan
SO Jpn. Kokai Tokkyo Koho, 6 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE	
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PI	JP 07014920	A2	19950117	JP 1993-147266	19930618	
AB	The devices are manufd. by (1) forming Al(-based alloy)-contg. under layer wirings having diffusion prevention layers comprising Ti nitride, Ti tungstide, or W nitride on substrates, (2) coating the layers with stopper layers comprising high-m.p. metal silicides, (3) coating the wirings with SiO ₂ -based interlayer insulating layers , (4) forming via-hole upper domains penetrating the layers by using resist masks with openings to bare the stopper layers , (5) removing of the masks, (6) removing of the bared stopper layers by using the interlayer layers as masks and the prevention layers as etch-stoppers by etching to bare the prevention layers and form via-holes , (7) optionally depositing amorphous thin films comprising amorphous Si , amorphous carbon , or Si ₃ N ₄ films sandwiched by SiO ₂ films on the interlayer layers to coat the via-holes , and (8) optionally coating the amorphous films with upper layer wirings to form antifuses comprising the amorphous films sandwiched by the under and upper layer wirin					

L64 ANSWER 21 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 1995:475907 HCAPLUS
 DN 123:45845
 TI Semiconductor device having **antifuse** structure of field
 programmable gate array and its manufacture
 IN Takagi, Mariko; Yoshii, Ichiro; Yasuda, Hiroo; Ikeda, Naoki; Hama, Kaoru
 PA Tokyo Shibaura Electric Co, Japan; Toshiba Micro Electronics
 SO Jpn. Kokai Tokkyo Koho, 11 pp.
 CODEN: JKXXAF

DT Patent
 LA Japanese

FAN.CNT 2

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 07022513	A2	19950124	JP 1993-190949	19930705
	CN 1107255	A	19950823	CN 1994-108287	19940705
	CN 1076123	B	20011212		
	US 5550400	A	19960827	US 1994-270458	19940705

PRAI JP 1993-190949 A 19930705

AB The device has (A) a semiconductor substrate **coated** with a 1st Al wiring elec. connected with a 1st electrode comprising a barrier metal for Al and a 2nd Al wiring elec. connected with a 2nd electrode comprising a barrier metal for Al and (B) a SiN0.6-1.2 **antifuse** film contacted with the both electrodes. The device has (A) a semiconductor substrate **coated** with a 1st Al wiring elec. connected with a barrier metal 1st electrode, (B) an elec. **insulating** film covered on the 1st wiring and the 1st electrode, (C) a SiN0.6-1.2 **antifuse** film contacted with the 1st electrode **via** a hole of the **insulating** film, (D) a monolayer or multilayer barrier metal 2nd electrode on the **antifuse** film, and (E) a 2nd Al wiring connected with the 2nd electrode on the substrate. The device is manufd. by forming a 1st Al wiring on a semiconductor substrate, forming a barrier metal 1st electrode elec. connected with the 1st wiring, forming an elec. **insulating** film on the 1st electrode and the 1st wiring, forming a hole in the **insulating** film, plasma chem. vapor depositing a SiN0.6-1.2 **antifuse** film contacted with the 1st electrode **via** the hole, forming a monolayer or multilayer barrier metal 2nd electrode on the **antifuse** film, and forming a 2nd Al wiring connected with the 2nd electrode on the substrate. The **antifuse** film showed lower dielec. const. than that of amorphous Si and high elec. resistivity. Hillock generation of the Al wiring was prevented.

L64 ANSWER 22 OF 30 HCAPLUS COPYRIGHT 2002 ACS

AN 1995:438087 HCAPLUS

DN 122:203166

TI **Antifuse** components and manufacturing thereof

PA Actel Corp., USA

SO Jpn. Kokai Tokkyo Koho, 12 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 6

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI	JP 06224304	A2	19940812	JP 1993-247539	19930908
	US 6001693	A	19991214	US 1995-999970	19950901
PRAI	US 1992-950264	A	19920923		
	US 1994-319170	A3	19941006		

AB The components have an **antifuse layer** formed in a multilayer **channel** and are prep'd. by (1) successively forming a lower electrode, a lower diffusion-barrier layer, a dielec. etching-stopper, and an isolating dielec. thick layer to give a laminated dielec. interlayer, (2) etching the dielec. interlayer to form a tapered channel to expose the lower electrode, (3) forming **antifuse** and upper diffusion-barrier layers provided in the channel, and (4) forming an upper electrode over the upper diffusion-barrier layer. The etching-stopper is Si₃N₄. The laminated interlayer dielec. layer may also have a SiO₂ layer. The use of the materials for the etching-stopper and the laminated interlayer dielec. layer gives the **antifuse** components a minimized contamination on the **antifuse** material during etching.

L64 ANSWER 23 OF 30 HCPLUS COPYRIGHT 2002 ACS

AN 1995:383068 HCPLUS

DN 122:149475

TI Semiconductor devices and their manufacture

IN Jinriki, Hiroshi; Kaizuka, Kenji; Oota, Tomohiro

PA Kawasaki Steel Co, Japan

SO Jpn. Kokai Tokkyo Koho, 7 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 3

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 06302700	A2	19941028	JP 1993-90318	19930419
	US 5521423	A	19960528	US 1994-228257	19940415
PRAI	JP 1993-90318		19930419		
	JP 1993-90319		19930419		
	JP 1993-92960		19930420		

AB The devices, contg. plural **antifuses**, consist of (A) the 2nd conductive wirings successively coated with (B) **insulating layers** having contact holes with **insulating films** consisting of oxides of Ti, Ta, Nb, Zr, Y, or Hf, (C) interlayer films, and (D) the 1st conductive wirings. Program devices, manufd. by puncturing the **insulating films** in the holes with resistance .ltoreq.200 .OMEGA., are also claimed. The manuf. involves (1) forming the **insulating layers** on the 1st conductive wirings comprising silicides of Ti, Ta, Nb, Zr, Hf, Co, Y, W, or Mo or Si, (2) forming the contact holes by patterning and etching, (3) forming the **insulating films**, (4) treating in acidic atm. to form the interlayer films with SiO₂ on the interfaces of the 1st wirings and the **insulating films**, and (5) forming patterns for the 2nd wirings on the **insulating films**.

ANSWER 24 OF 30 HCPLUS COPYRIGHT 2002 ACS

AN 1995:354704 HCPLUS

DN 122:149444

TI Metal-to-metal **antifuse** including etch stop layer

IN Chen, Wenn Jei; Chiang, Steve S.; Hawley, Frank W.

PA USA

SO U.S., 6 pp. Cont.-in-part of U.S. Ser. No. 950,264, abandoned.
CODEN: USXXAM

DT Patent
LA English
FAN.CNT 6

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 5381035	A	19950110	US 1993-172132	19931221
	US 5614756	A	19970325	US 1994-284054	19940801
	US 5525830	A	19960611	US 1994-322871	19941012

AB Planar layers of nitride (1st nitride layer), a-Si (1st a-Si layer), nitride (2nd nitride layer) and a-Si (2nd a-Si layer) are laid down over a 1st metalization layer. A dielec. layer is then laid down on top of the 2nd a-Si layer. A via is opened in the dielec. layer with an etch gas which attacks a small portion of the 2nd a-Si layer which, in effect, serves as a sacrificial etch-stop layer. A Ti layer is laid down over the via and allowed to thermally react with the remainder of the 2nd a-Si layer to form an elec. conductive Ti silicide region in the area of the via the thickness of the 2nd a-Si layer. The reaction is self-limiting and stops at the 2nd nitride layer. Subsequently a 2nd metalization layer is disposed over the via. Thus the partially etched 2nd a-Si layer forms a part of the 2nd metalization layer and the nitride/a-Si/nitride insulating antifuse layer has a const. thickness detd. by the process used to lay it down, rather than on the more uncontrollable etch process. Accordingly, the programming voltage of the antifuse is more predictable than with prior art antifuse structures.

L64 ANSWER 25 OF 30 HCAPLUS COPYRIGHT 2002 ACS

AN 1995:347311 HCAPLUS

DN 122:120952

TI Semiconductor device and its manufacture
IN Jinriki, Hiroshi; Kaizuka, Kenji; Oota, Tomohiro
PA Kawasaki Steel Co, Japan
SO Jpn. Kokai Tokkyo Koho, 7 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 3

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 06310687	A2	19941104	JP 1993-92960	19930420
	US 5521423	A	19960528	US 1994-228257	19940415

PRAI JP 1993-90318

19930419

JP 1993-90319

19930419

JP 1993-92960

19930420

AB In the title device having antifuses, the insulator films of the antifuse consist of a Si film formed by vapor deposition, and multilayers of a SiO₂ layer and Ti, Ta, Nb, Zr, Y, Hf, or Al oxide layer. Alternatively, Ti, Ta, Nb, Zr, Y, and/or Hf nitride or TiB or TiC may exist between the 1st metal layer and the insulator films of the antifuse. The title manuf. involves the following steps: (1) forming insulator films on the 1st metal wiring, (2) opening a contact-hole, (3) depositing an amorphous Si on the insulator films by decompg. SiH₄ gas with a high frequency at a low pressure, (4) depositing a metal oxide film by thermally decompg.

Ti, Ta, Nb, Zr, Y, or Hf alkoxide steam in an oxidizing atm. at a low pressure to form SiO₂ film between the amorphous Si and the metal oxide film, and (5) forming the 2nd metal wiring.

L64 ANSWER 26 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 1993:660663 HCAPLUS
 DN 119:260663
 TI Programmable ROM anti-fuse semiconductor devices and fabrication thereof
 IN Myajima, Motomori
 PA Fujitsu Ltd, Japan
 SO Jpn. Kokai Tokkyo Koho, 5 pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 05090527	A2	19930409	JP 1991-249232	19910927

PI AB The title device employs an amorphous Si semiconductor layer which is formed only in its through-hole connecting between an upper and lower circuit layers. The title amorphous Si layer formed only in the through hole and not on the interlayer insulator film gives its step height decreased

L64 ANSWER 27 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 1993:572182 HCAPLUS
 DN 119:172182
 TI Manufacture of antifuse region-contg. semiconductor device
 IN Ootsuki, Masaya
 PA Fujitsu Ltd, Japan
 SO Jpn. Kokai Tokkyo Koho, 5 pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 05121556	A2	19930518	JP 1991-281790	19911029

PI AB The device is manufd. by: (1) forming an elec. insulating film on a 1st elec. conducting layer; (2) forming a contact-hole to reach the conducting layer; (3) forming a 2nd elec. conducting layer; (4) patterning the 2nd conducting layer to remove except in the hole; (5) implanting impurity ion into the 2nd conducting layer in the hole for an antifuse region to give an amorphous layer; and (6) forming a 3rd elec. conducting layer on the 2nd conducting layer and the amorphous layer. Implantation may be done before patterning. The 2nd conducting layer showed good contact for the 3rd conducting layer

L64 ANSWER 28 OF 30 HCAPLUS COPYRIGHT 2002 ACS
 AN 1993:572181 HCAPLUS
 DN 119:172181
 TI Manufacture of antifuse region-contg. electric circuit and programmable read only memory (PROM)
 IN Tsuzuki, Norihisa
 PA Fujitsu Ltd, Japan

SO Jpn. Kokai Tokkyo Koho, 4 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI JP 05121555 A2 19930518 JP 1991-181105 19910722

AB The circuit and PROM is manufd. by depositing a 1st elec. insulating film on an elec. conducting substrate, forming a hole to reach the substrate, forming an amorphous Si layer near the hole, depositing a Pt layer, reacting the Si layer and the Pt layer to form a Pt silicide layer, removing the unreacted Pt layer, depositing a 2nd elec. insulating film, and forming a contact-hole to reach the silicide layer. Over-etching of the amorphous Si layer was prevented.

L64 ANSWER 29 OF 30 HCAPLUS COPYRIGHT 2002 ACS

AN 1993:572179 HCAPLUS

DN 119:172179

TI Manufacture of antifuse region-contg. semiconductor device

IN Fujiwara, Yukio

PA Fujitsu Ltd, Japan

SO Jpn. Kokai Tokkyo Koho, 4 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI JP 05121552 A2 19930518 JP 1991-278013 19911024

AB The device is manufd. by forming a lower wiring on a substrate, forming an interlayer insulating film, patterning the insulating film for removal, forming a contact-hole, forming an amorphous Si layer in the hole for an antifuse region, oxidizing the Si layer to form a Si oxide film, irradiating with inert gas ion to remove deposits in the hole and the oxide film except the antifuse region, and forming an upper wiring on the insulating film. The amorphous Si layer had low defects.

L64 ANSWER 30 OF 30 HCAPLUS COPYRIGHT 2002 ACS

AN 1993:572167 HCAPLUS

DN 119:172167

TI Manufacture of an anti-fuse semiconductor device

IN Fujiwara, Yukio

PA Fujitsu Ltd, Japan

SO Jpn. Kokai Tokkyo Koho, 3 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI JP 05114651 A2 19930507 JP 1991-275685 19911023
AB The device is manufd. by forming an underlayer wiring on a substrate,
forming an interlayer insulating film, patterning the
insulating film to remove and form a contact-
hole, forming an **amorphous Si layer**
on the insulating film, etching the Si layer
except for an **anti-fuse** region to reduce the thickness
of the Si layer and form an **amorphous Si**
thin film, irradiating with inert gas ion to remove the
amorphous Si, and forming an upper wiring on the
insulating film. The device showed good step coverage.

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File 2:INSPEC 1969-2002/Jan W1
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File 6:NTIS 1964-2002/Jan W3
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*File 6: See HELP CODES6 for a short list of the Subject Heading Codes
(SC=, SH=) used in NTIS.

File 8:Ei Compendex(R) 1970-2002/Jan W1
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File 34:SciSearch(R) Cited Ref Sci 1990-2002/Jan W1
(c) 2002 Inst for Sci Info

File 434:SciSearch(R) Cited Ref Sci 1974-1989/Dec
(c) 1998 Inst for Sci Info

File 35:Dissertation Abs Online 1861-2001/Dec
(c) 2001 ProQuest Info&Learning

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(c) 2001 Cambridge Sci Abs

File 94:JICST-EPlus 1985-2002/Nov W4
(c) 2002 Japan Science and Tech Corp (JST)

*File 94: There is no data missing. UDs have been adjusted to reflect
the current months data. See Help News94 for details.

File 99:Wilson Appl. Sci & Tech Abs 1983-2001/Nov
(c) 2001 The HW Wilson Co.

File 108:AEROSPACE DATABASE 1962-2001/DEC
(c) 2001 AIAA

*File 108: For update information please see Help News108.

File 144:Pascal 1973-2002/Dec W5
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See HELP NEWS 305.

File 315:ChemEng & Biotec Abs 1970-2001/Oct
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*File 65: For variance in UDs please see Help News65.

Set	Items	Description
S1	6591	CI=(SI SS(S) O SS) (S) NE=2
S2	2668	CI=(SI SS(S) N SS) (S) NE=2
S3	2045	CI=(SI SS(S) N SS(S) O SS) (S) NE=3
S4	189712	SILICON(W)OXIDE OR SI(W)OXIDE OR SIO OR (OXOSILYLENE(W)28SI) OR (SILICON (N) MONOXIDE) OR (SILICON(2N) MONOXIDE)
S5	105043	SILICON(W)NITRIDE OR SI(W)NITRIDE OR SIN OR (SILICON(2N) M-ONONITRIDE)
S6	5427	(SILICON (N)NITRIDE(N) .OXIDE) OR (SILICON (N)NITRIDE(N) OXIDE) OR (DISILICON(N) OXYDINITRIDE) OR (DISILICON(N) OXYNITRIDE) OR (SILICON(N)OXYNITRIDE) OR (SI(N) OXYNITRIDE? ?)
S7	132271	DIAMOND OR (DIAMOND(3N)CARBON)
S8	1124	(FLUORIN?) (W) (DOP?) (W) (OXIDE?) OR (FLUORIN?) (2N) (OXIDES)
S9	1026	F(W)DOP???
S10	1289	(ANTI (2W)FUSE? ?) OR ANTIFUSE? ? OR OTP OR ((ONE) (N) (TIME)- (N) (PROGRAM?))
S11	375051	(DIELECTRIC? OR OXIDE OR INSULAT?) (3N) (FILM? ? OR LAYER? OR COAT???? OR MATERIAL?)
S12	1141588	((ANTI(N)REFLECT?) (2N) (COAT???? OR FILM? ? OR LAYER?)) OR ((DICHROIC) (2N) (FILTER? OR MIRROR)) OR (FRESNEL(W)REFLECT?) - OR REFLECT?
S13	93494	(POLYIMIDE? ? OR POLYAMIDE? ? OR PARYLENE OR PARALYENE)
S14	2636003	(ALUMINUM OR AL OR TUNGSTEN OR W)
S15	2780510	(COPPER OR CU OR CHROMIUM OR CR OR GOLD OR AU)
S16	620083	(PLATINUM OR PT OR PALLADIUM OR PD)
S17	692537	(SELENIUM OR SE OR GERMANIUM OR GE)
S18	2116	S8 OR S9
S19	73	S10 AND S11
S20	12	S19 AND (VIAS OR VIA OR TRENCH? OR HOLE? ? OR CHANNEL OR G- ROOVE? OR EDGE? OR FLUSH?)
S21	33	S19 AND (S1 OR S2 OR S4 OR S5 OR S7 OR S18)
S22	0	S19 AND (S13 OR POLYMETHYLACRYLATE)
S23	36	S19 AND (S13 OR S14 OR S15 OR S16)
S24	107468	AMORPHOUS(2N) (SI OR SILICON OR C OR CARBON)
S25	9	S19 AND (S24 OR S17 OR COMPOUND(W)SEMICONDUCTOR? ? OR CERAMIC? ? OR S12 OR S6 OR S3)
S26	0	S20 AND S21 AND S23 AND S25
S27	0	S21 AND S23 AND S25
S28	25	S21 AND S23
S29	44	S21 OR S23
S30	31	RD (unique items)
S31	41	S30 OR S20 OR S25
S32	38	RD (unique items)
S33	38	S32 NOT PD>=20010604

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>>>No matching display code(s) found in file(s): 65

33/3,AB/1 (Item 1 from file: 2)
DIALOG(R)File 2:INSPEC
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6747320 INSPEC Abstract Number: B2000-12-2530G-001
Title: Breakdown mechanism of Al₂O₃/sub 3/ based metal-to-metal
antifuses

Author(s): Wei-Tang Li; McKenzie, D.R.; McFall, W.D.; Qi-Chu Zhang; Wiszniewski, W.

Author Affiliation: Dept. of Appl. Phys., Sydney Univ., NSW, Australia
Journal: Solid-State Electronics vol.44, no.9 p.1557-62

Publisher: Elsevier,
Publication Date: Sept. 2000 Country of Publication: UK

CODEN: SSELAS ISSN: 0038-1101

SICI: 0038-1101(200009)44:9L.1557:BMAB;1-Z

Material Identity Number: S068-2000-009

U.S. Copyright Clearance Center Code: 0038-1101/2000/\$20.00

Language: English

Abstract: An impulse thermal breakdown model is proposed to understand the breakdown mechanism of Al₂O₃/sub 3/ thin film based metal-to-metal antifuses. In this model, the electric field dependence as well as the temperature dependence of the electrical conductivity is considered. The I-V characteristic of the antifuses indicated that the conductivity of Al₂O₃/sub 3/ rose greatly under high field. The threshold breakdown voltage of the antifuses was shown by experiment to be proportional to its insulator thickness and to the square root of the insulator resistivity. When breakdown of the antifuses was carried out by applying constant voltage pulse, the inverse square root of the time to breakdown was shown to be proportional to the amplitude of the pulse. All the experimental results were found to be consistent with the theoretical results of the model. In addition, an antifuse breakdown filament with a diameter of 150 nm was observed by using a scanning electron microscope.

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33/3,AB/2 (Item 2 from file: 2)

DIALOG(R)File 2:INSPEC

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6260720 INSPEC Abstract Number: B1999-07-2530G-001

Title: Effect of different barrier materials on antifuse performance

Author(s): Ang, T.C.; Tse, M.S.; Chan, L.; Sudijono, J.L.

Author Affiliation: Sch. of Electr. & Electron. Eng., Nanyang Technol. Inst., Singapore

Journal: Proceedings of the SPIE - The International Society for Optical Engineering Conference Title: Proc. SPIE - Int. Soc. Opt. Eng. (USA) vol.3510 p.233-9

Publisher: SPIE-Int. Soc. Opt. Eng,

Publication Date: 1998 Country of Publication: USA

CODEN: PSISDG ISSN: 0277-786X

SICI: 0277-786X(1998)3510L.233:EDBM;1-#

Material Identity Number: C574-1998-269

U.S. Copyright Clearance Center Code: 0277-786X/98/\$10.00

Conference Title: Microelectronic Manufacturing Yield, Reliability, and Failure Analysis IV

Conference Sponsor: SPIE

Conference Date: 23-24 Sept. 1998 Conference Location: Santa Clara, CA, USA

Language: English

Abstract: An **antifuse** is a programmable interconnect element used in field programmable gate arrays (FPGAs). It is made up of an insulating layer sandwiched by 2 electrodes. The device is normally off and has a high resistance when unprogrammed. However, with the application of a programming voltage or current pulse, the **antifuse** turns into a 'fuse' of low resistance due to the breakdown of the insulator, accompanied by the formation of a conductive path or filament through the insulating layer. Metal to metal **antifuses** are favored for high speed and high density FPGAs because they offer low on-resistance, small device area and high reliability. In FPGAs incorporating **antifuses**, there are typically thousands of **antifuses** and their leakage currents are quite substantial, thereby leading to considerable power consumption. Leakage current, I_{sub} leakage/reduction can be achieved through the discerning choice of electrodes, **antifuse** stack material, stack composition, thickness and film deposition process conditions amongst others. In this paper, the electrical characteristics of the **amorphous silicon-based antifuse** with different types of barrier layers are presented. We show that the inclusion of an in-situ top barrier layer in the a-Si:H based **antifuse** leads to a significant reduction in the leakage current with no appreciable increase in the programming voltage.

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33/3,AB/3 (Item 3 from file: 2)

DIALOG(R)File 2:INSPEC

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6194619 INSPEC Abstract Number: B1999-04-2190-001

Title: Metal-to-metal **antifuse** with amorphous Ti-rich barium titanate film and silicon oxide film

Author(s): Jae Sung Lee; Young Hyun Lee

Author Affiliation: Dept. of Comput. & Commun. Eng., Uiduk Univ., Kyongbuk, South Korea

Journal: Solid-State Electronics vol.43, no.3 p.469-72

Publisher: Elsevier,

Publication Date: March 1999 Country of Publication: UK

CODEN: SSELA5 ISSN: 0038-1101

SICI: 0038-1101(199903)43:3L.469:MMAW;1-4

Material Identity Number: S068-1999-001

U.S. Copyright Clearance Center Code: 0038-1101/99/\$20.00

Language: English

Abstract: This paper is focused on the fabrication of reliable novel **antifuse**, which could operate at low voltage along with the improvement in off and on-state properties. An **antifuse** composed of Ti-rich barium titanate/silicon oxide sandwiched between Al and TiW-silicide has been developed for high reliable field programmable devices. The breakdown voltage of an **antifuse** is properly reduced by using amorphous Ti-rich barium titanate film and leakage current is not significantly increased due to the high quality of silicon oxide. Low on-resistance (46 Omega / mu m²) and low programming voltage (9 V) is demonstrated in these **antifuses** with

a 220 AA double insulator layer while keeping sufficient off-state reliability. A significant capacitance reduction at high operating frequencies is also realized.

Subfile: B

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33/3,AB/4 (Item 4 from file: 2)

DIALOG(R)File 2:INSPEC

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6064678 INSPEC Abstract Number: B9812-1265B-020

Title: **Antifuse with Ti-rich barium titanate film and silicon oxide film**

Author(s): Lee, J.S.; Lee, Y.H.

Journal: Journal of the Institute of Electronics Engineers of Korea D vol.35-D, no.7 p.72-8

Publisher: Inst. Electron. Eng. Korea,

Publication Date: July 1998 Country of Publication: South Korea

CODEN: CKODF8 ISSN: 1226-5845

SICI: 1226-5845(199807)35D:7L.72:AWRB;1-B

Material Identity Number: G412-98008

Language: Korean

Abstract: This paper is focused on the fabrication of a reliable novel **antifuse**, which could operate at low voltage and provide an improvement in OFF and ON-state properties in an FPGA. The fabricated **antifuse** consists of a $\text{Al-BaTi}/\sub{2}/\text{O}/\sub{3}/\text{-SiO}/\sub{2}/\text{-TiW}$ -silicide structure. Through systematic analyses for bottom metal and the intermetallic **insulator**, **material** and electrical properties were investigated. TiW-silicide as the bottom electrode had a smooth surface with average roughness of 11 AA at $10*10 \mu\text{m}^2$ and kept the as-deposited SiO_2 film stable. The amorphous $\text{BaTi}/\sub{2}/\text{O}/\sub{3}/$ film was chosen as the other insulator because of its low breakdown strength (2.5 MV/cm). The breakdown voltage of the **antifuse** is remarkably reduced by using a $\text{BaTi}/\sub{2}/\text{O}/\sub{3}/$ film, and leakage current is maintained at that low level due to the SiO_2 film. Low ON-resistance ($46 \Omega/\mu\text{m}^2$) and low programming voltage (9.1 V) can be obtained in these **antifuses** with a 220 AA double insulator layer and $19.6*10^{-6}/\text{cm}^2$ area, while keeping sufficient OFF-state reliability (less than 1 nA).

Subfile: B

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33/3,AB/5 (Item 5 from file: 2)

DIALOG(R)File 2:INSPEC

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5452319 INSPEC Abstract Number: B9702-2530G-001

Title: **High performance antifuse with planar double dielectrics on $\text{Si}/\sub{1-x}/\text{Ge}/\sub{x}$ pad for field programmable gate array applications**

Author(s): Kim, J.; Park, M.Y.; Song, Y.H.; Baek, J.T.

Author Affiliation: Semicond. Div., Electron. & Telecommun. Res. Inst., Taejon, South Korea

Journal: Electronics Letters vol.32, no.24 p.2276-7

Publisher: IEE,

Publication Date: 21 Nov. 1996 Country of Publication: UK

CODEN: ELLEAK ISSN: 0013-5194

SICI: 0013-5194(19961121)32:24L.2276:HPAW;1-C

Material Identity Number: E089-96024

U.S. Copyright Clearance Center Code: 0013-5194/96/\$10.00

Language: English

Abstract: A new **antifuse** device with a planar metal/dielectric/poly-Si/_{1-x}Ge/_x/dielectric/metal structure has been proposed for use in FPGAs as a voltage programmable link. The device has low leakage current (~0.01 pA/antifuse) at an operating voltage of 5 V and low on-resistance (~13-15 Omega) with a 1 ms long 12.5 V pulse.

Subfile: B

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33/3,AB/6 (Item 6 from file: 2)

DIALOG(R)File 2:INSPEC

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5447917 INSPEC Abstract Number: B9701-2550F-038

Title: Device characteristics and metal link formation in the planar **antifuse** with poly-Si pad

Author(s): Baek, J.T.; Jung, S.H.; Kang, S.W.; Ahn, B.T.

Author Affiliation: Dept. of Mater. Sci. & Eng., Korea Adv. Inst. of Sci. & Technol., Seoul, South Korea

Journal: Journal of the Korean Institute of Telematics and Electronics vol.33A, no.8 p.158-66

Publisher: Korea Inst. Telematics & Electron,

Publication Date: Aug. 1996 Country of Publication: South Korea

CODEN: CKNOEZ ISSN: 1016-135X

SICI: 1016-135X(199608)33A:8L.158:DCML;1-J

Material Identity Number: N523-96024

Language: Korean

Abstract: The programming phenomena of an **antifuse** device with a planar Al-SiO/₂-polysilicon-SiO/₂-Al structure were investigated using a parameter analyzer, an optical microscope and a scanning electron microscope. When the breakdown voltage was applied, one or two holes were formed on the SiO/₂/layer by oxide breakdown and Al flowed through the holes into the poly Si layer. With further application of voltage after breakdown, Al from the positive electrode flowed into the poly-Si layer and the two electrodes were connected by AlSi alloy. The resistances of the device before and after oxide breakdown were a few G Omega and about 1 k Omega, respectively. Furthermore, the resistance drastically reduced to nearly 30 Omega after forming the AlSi conducting line between the two electrodes. The conducting line between the two electrodes grew a few cm/sec when the applied voltage was above the critical voltage. The critical voltage was proportional to the length of devices, indicating that critical current exists. The measured critical current was about 8 mA when the width of the device was 2.4 mu m. It is supposed that the polysilicon in front of the conducting line was partially melted by Joule heating caused by current crowding, and fast growth of the conducting line was possible.

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33/3,AB/7 (Item 7 from file: 2)

DIALOG(R)File 2:INSPEC

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5345383 INSPEC Abstract Number: B9609-2550F-039

Title: The interfacial properties of the annealed $\text{SiO}_{\text{sub}} 2$ / -TiW structure

Author(s): Jae Sung Lee; Hyung Ho Park; Jung Hee Lee; Yong Hyun Lee

Author Affiliation: Dept. of Electr. Eng., Kyungpook Nat. Univ., Taegu, South Korea

Journal: Journal of the Korean Institute of Telematics and Electronics vol.33A, no.3 p.117-25

Publisher: Korea Inst. Telematics & Electron,

Publication Date: March 1996 Country of Publication: South Korea

CODEN: CKNOEZ ISSN: 1016-135X

SICI: 1016-135X(199603)33A:3L.117:IPAS;1-0

Material Identity Number: N523-96014

Language: Korean

Abstract: The variation of the interfacial and the electrical properties of $\text{SiO}_{\text{sub}} 2$ / -TiW layers as a function of anneal temperature was extensively investigated. During the deposition of $\text{SiO}_{\text{sub}} 2$ / on TiW, chemical bonds such as $\text{SiO}_{\text{sub}} 2$ /, TiW, $\text{WO}_{\text{sub}} 3$ /, $\text{WO}_{\text{sub}} 2$ /, $\text{TiO}_{\text{sub}} 2$ /, $\text{Ti}_{\text{sub}} 2\text{O}_{\text{sub}} 3$ / and/or $\text{Ti}_{\text{sub}} 3\text{O}_{\text{sub}} 5$ / were created at the $\text{SiO}_{\text{sub}} 2$ / -TiW interface. At the anneal temperature of 300 degrees C, $\text{WO}_{\text{sub}} 3$ / and $\text{TiO}_{\text{sub}} 2$ / bonds began to break due to the reduction phenomena of W and Ti, and simultaneously metallic W and Ti bonds started to create. Above 500 degrees C, part of the Si-O bonds were broken, and consequently Ti/W silicide was formed. From the current-voltage characteristics of the Al- $\text{SiO}_{\text{sub}} 2$ / (220 AA)-TiW antifuse structure, it was found that the breakdown voltage of the antifuse device decreased with increasing annealing temperature for the $\text{SiO}_{\text{sub}} 2$ / (220 AA)-TiW layer, when the insulating properties of the antifuse device were affected by the deterioration of the intermetallic $\text{SiO}_{\text{sub}} 2$ / film caused by the inflow of Ti and W.

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33/3,AB/8 (Item 8 from file: 2)

DIALOG(R)File 2:INSPEC

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5264116 INSPEC Abstract Number: B9606-2190-001

Title: Extremely low ON-resistance metal-to-metal antifuses with Al-Cu/10 nm-thick p-SiN_x / / Al-Cu structure for next generation very high speed FPGAs (field programmable gate arrays)

Author(s): Tamura, Y.; Kimura, Y.; Tsutsui, C.; Shinriki, H.

Author Affiliation: Adv. Technol. Res. Section, Kawasaki Steel Corp., Chiba, Japan

Journal: Japanese Journal of Applied Physics, Part 1 (Regular Papers & Short Notes) Conference Title: Jpn. J. Appl. Phys. 1, Regul. Pap. Short Notes (Japan) vol.35, no.2B p.1049-53

Publisher: Publication Office, Japanese Journal Appl. Phys,

Publication Date: Feb. 1996 Country of Publication: Japan

CODEN: JAPNDE ISSN: 0021-4922

SICI: 0021-4922(199602)35:2BL.1049:ERMM;1-X

Material Identity Number: C579-96005

Conference Title: 1995 International Conference on Solid State Devices and Materials (SSDM '95)

Conference Date: 21-24 Aug. 1995 Conference Location: Osaka, Japan

Language: English

Abstract: We present a novel metal-to-metal **antifuse** structure consisting of a plasma enhanced CVD (chemical vapor deposition) silicon nitride ($p\text{-SiN}/\text{sub } x$) dielectric film sandwiched between two **aluminum** layers. The leakage current in the off-state is markedly reduced by using **aluminum** film as the upper electrode instead of Ti(titanium) or TiN(titanium nitride) film. A Al-Cu/10 nm-thick $p\text{-SiN}/\text{sub } x$ //Al-Cu structure **antifuse** provides sufficient long-term off-state reliability exceeding ten years at 3.6 V while keeping low breakdown voltage (10 V). An extremely low on-resistance of around 3 Omega and a narrow distribution are also realized. A new **antifuse** structure ($\text{Al-Cu}/p\text{-SiN}/\text{sub } x/\text{Al-Cu}(100 \text{ nm})/\text{Ti/TiN}/\text{Al-Cu}$) highly compatible with the conventional **via** formation process in double metal interconnect wiring is proposed. This type of **antifuse** structure is very promising for next-generation very high-speed FPGAs.

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33/3,AB/9 (Item 9 from file: 2)
DIALOG(R)File 2:INSPEC
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5165891 INSPEC Abstract Number: A9604-6848-004, B9603-2530G-001
Title: Interfacial reaction in the sputter-deposited $\text{SiO}_2/\text{Ti}/\text{sub } 0.1/\text{W}/\text{sub } 0.9/\text{antifuse}$ system
Author(s): Jong Tae Baek; Hyung-Ho Park; Kyung-Ik Cho; Hyung Joun Yoo; Sang Won Kang; Byung Tae Ahn
Author Affiliation: Semicond. Technol. Div., Electron. & Telecommun. Res. Inst., Taejon, South Korea
Journal: Journal of Applied Physics vol.78, no.12 p.7074-9
Publisher: AIP,
Publication Date: 15 Dec. 1995 Country of Publication: USA
CODEN: JAPIAU ISSN: 0021-8979
SICI: 0021-8979(19951215)78:12L.7074:IRSD;1-K
Material Identity Number: J004-96001
U.S. Copyright Clearance Center Code: 0021-8979/95/78(12)/7074/6/\$6.00
Language: English

Abstract: The effects of annealing temperature on the interfacial reactions and the **antifuse** I-V characteristics of ultra thin $\text{SiO}_2/\text{Ti}/\text{sub } 0.1/\text{W}/\text{sub } 0.9/\text{substrate}$ were investigated. The interfacial reactions were analyzed using X-ray photoelectron spectroscopy and Auger electron spectroscopy with the sample which is in situ annealed under ultra high vacuum or ex situ annealed in a nitrogen atmosphere. The surface of the $\text{Ti}/\text{sub } 0.1/\text{W}/\text{sub } 0.9/\text{substrate}$ was oxidized during sputter deposition of $\text{SiO}_2/\text{Ti}/\text{sub } 0.1/\text{W}/\text{sub } 0.9/\text{substrate}$. Ti, W oxides consist of $\text{Ti}/\text{sub } 2/\text{O}/\text{sub } 3/\text{(Ti}/\text{sub } 3/\text{O}/\text{sub } 5/)$, $\text{TiO}/\text{sub } 2/$, $\text{WO}/\text{sub } 2/$, and $\text{WO}/\text{sub } 3/$. The $\text{WO}/\text{sub } 3/$ and $\text{Ti}/\text{sub } 2/\text{O}/\text{sub } 3/$ decomposed into metallic W and Ti at 400 and 500 degrees C, respectively. The breakdown voltage of the **antifuse** decreased as the annealing temperature increased, due to the thinning of the dielectric layer resulting from the decomposition of Ti, W oxides and the formation of metallic W and Ti. Annealing at 600 degrees C caused the reaction between metallic (Ti,W) and the $\text{SiO}_2/\text{Ti}/\text{sub } 0.1/\text{W}/\text{sub } 0.9/\text{substrate}$ and formed elemental silicon in the dielectric layer, where the $\text{SiO}_2/\text{Ti}/\text{sub } 0.1/\text{W}/\text{sub } 0.9/\text{substrate}$ completely lost its dielectric property the breakdown of dielectric property might form a

metallic channel in the SiO₂/sub 2/ film, which mainly contains metallic W, Ti, and Si.

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33/3,AB/10 (Item 10 from file: 2)
DIALOG(R)File 2:INSPEC
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5090856 INSPEC Abstract Number: B9512-2570-012
Title: Ultra clean processing for ULSI
Author(s): Ohmi, T.
Author Affiliation: Dept. of Electron., Tohoku Univ., Sendai, Japan
Journal: Microelectronics Journal vol.26, no.6 p.595-619
Publication Date: Sept. 1995 Country of Publication: UK
CODEN: MICEB9 ISSN: 0026-2692
U.S. Copyright Clearance Center Code: 0026-2692/95/\$9.50

Language: English

Abstract: The simultaneous fulfilment of three principles, viz. ultraclean water surface, ultra-clean processing environment, and perfect process-parameter control, is the key to high-performance fabrication of advanced subhalf-micron and subquarter-micron ULSI devices. The importance of this ultra-clean processing concept is demonstrated by the experimental results of low-temperature silicon epitaxy by low-kinetic-energy Ar ion bombardment. By optimizing process parameters under ultra-clean conditions, high-crystallinity silicon epitaxial layers are successfully grown at temperatures as low as 250 degrees C, with accompanying simultaneous doping. Advanced copper metallization for large-current driving interconnect is also achieved. Giant-grain copper thin films, also formed by low-kinetic-energy Ar ion bombardment, exhibit very low resistivity and excellent reliability against electromigration and stress migration. Native and chemical-oxide-free processing produces ideal metal-to-silicon contacts with very low resistance, i.e. 10⁻⁹ Omega .cm². Ultra-clean-hydrogen-radical-balanced and surface-microroughness-free-oxidation is confirmed to form high quality, very thin oxide films of 5 to 10 nm, with complete uniformity and very strong resistance to hot electron injection. Low-temperature annealing ion implantation makes practical a metal gate self-aligned MOS LSI, which is crucial for high current driving capability in high-speed CMOS. All of these advanced fabrication technologies, realized for the first time by ultraclean techniques, allow total low-temperature processing, such as gate oxidation at 450 degrees C, implanted region annealing at 450 degrees C and single-crystal silicon epitaxy at 300 degrees C, which is essential for high-performance subhalf-micron and subquarter-micron ULSI. Oxide layer-free metal-to-silicon and metal-to-metal film deposition is freely available in ultra-clean processes, so that field-programmable anti-fuse technology is achievable by current drive silicidation as well as by very low resistance metal/silicon and metal/metal contact.

Subfile: B
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33/3,AB/11 (Item 11 from file: 2)
DIALOG(R)File 2:INSPEC
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4941924 INSPEC Abstract Number: B9506-2530G-003

Title: Relation between stress-induced leakage current and dielectric breakdown in SiN-based antifuses

Author(s): Yasuda, H.; Ikeda, N.; Hama, K.; Takagi, M.T.; Yoshii, I.

Author Affiliation: Semicond. Device Eng. Lab., Toshiba Corp., Kawasaki, Japan

Journal: Japanese Journal of Applied Physics, Part 1 (Regular Papers & Short Notes) vol.34, no.3 p.1488-92

Publication Date: March 1995 Country of Publication: Japan

CODEN: JAPNDE ISSN: 0021-4922

Language: English

Abstract: We report on the degradation process of metal-to-metal antifuses that use thin silicon nitride film as the dielectric layer under high electric held stress.

Stress-induced leakage current was observed in all samples, and it flows through local spots. Two-level fluctuations were found on the leakage current well below the stress voltage, and large and complex fluctuations were observed near the stress voltage. The conduction mechanism of the stress-induced leakage current was the Poole-Frenkel type. It was found that the dielectric constant of the path became large and that the breakdown and the anomalous current depended on the barrier metal thickness. Considering these results, the stress-induced leakage current and the breakdown are thought to be caused by electromigration of electrode material to the SiN film.

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33/3,AB/12 (Item 12 from file: 2)

DIALOG(R)File 2:INSPEC

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4886259 INSPEC Abstract Number: B9504-1265B-042

Title: Most promising metal-to-metal antifuse based 10 nm-thick p-SiN_x/ film for high density and high speed FPGA application

Author(s): Tamura, Y.; Shinriki, H.

Author Affiliation: LSI Res. Lab., Kawasaki Steel Corp., Chiba, Japan p.285-8

Publisher: IEEE, New York, NY, USA

Publication Date: 1994 Country of Publication: USA 947 pp.

ISBN: 0 7803 2111 1

U.S. Copyright Clearance Center Code: 0 7803 2111 1/94/\$4.00

Conference Title: Proceedings of 1994 IEEE International Electron Devices Meeting

Conference Sponsor: Electron Devices Soc. IEEE

Conference Date: 11-14 Dec. 1994 Conference Location: San Francisco, CA, USA

Language: English

Abstract: A novel metal-to-metal antifuse has been developed for highly reliable and high performance 3.3 V operated FPGAs. Dielectric breakdown reliability is remarkably improved by using amorphous-like WS_x/ film as a bottom electrode having extremely smooth surface. Sufficient low ON-resistance (8.2 Ω) and low programming voltage (9 V) can be also obtained in the metal-to-metal antifuses having WS_x/SiN_x/(10 nm)/TiN structure while keeping sufficient OFF-state reliability. By using WS_x/SiN_x/Al-Cu structure, lowest ON-resistance (2 Ω) can be obtained. These metal-to-metal antifuse structures are very promising for next generation FPGAs.

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33/3,AB/13 (Item 13 from file: 2)
DIALOG(R)File 2:INSPEC
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4767690 INSPEC Abstract Number: B9411-2530N-001
Title: Metal-to-metal **antifuses** with very thin silicon dioxide films
Author(s): Zhang, G.; Hu, E.; Yu, P.; Chiang, S.; Hamdy, E.
Author Affiliation: Dept. of Phys., California Univ., Berkeley, CA, USA
Journal: IEEE Electron Device Letters vol.15, no.8 p.310-12
Publication Date: Aug. 1994 Country of Publication: USA
CODEN: EDLEDZ ISSN: 0741-3106
U.S. Copyright Clearance Center Code: 0741-3106/94/\$04.00

Language: English
Abstract: **Antifuse** samples with very thin insulating oxide were fabricated using a technique of two-step PECVD oxide deposition. Dielectric strength as high as 13 MV/cm was obtained for our samples. Defect density and uniformity have been improved in this way. The on-state resistance of the programmed **antifuses** shows a stronger dependence on the oxide thickness when it was programmed at the lower current than when it was programmed at the higher current.

Subfile: B

33/3,AB/14 (Item 14 from file: 2)
DIALOG(R)File 2:INSPEC
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04353413 INSPEC Abstract Number: B9304-2550E-027
Title: Conductive **channel** in ONO formed by controlled dielectric breakdown
Author(s): Chiang, S.; Wang, R.; Speers, T.; McCollum, J.; Hamdy, E.; Hu, C.
Author Affiliation: Actel Corp., Sunnyvale, CA, USA
Conference Title: 1992 Symposium on VLSI Technology. Digest of Technical Papers (Cat. No.92CH3172-4) p.20-1
Publisher: IEEE, New York, NY, USA
Publication Date: 1992 Country of Publication: USA x+120 pp.
ISBN: 0 7803 0698 8
U.S. Copyright Clearance Center Code: 92CH3172-4/92/0000-0020\$03.00
Conference Sponsor: IEEE; Japan Soc. Appl. Phys
Conference Date: 2-4 June 1992 Conference Location: Seattle, WA, USA
Language: English

Abstract: Cross-section TEM photos that capture the conductive **channel** of **oxide-nitride-oxide** (ONO) **films** after electric breakdown are discussed. The photos reveal a single crystal or polycrystal **channel** with a dome-shaped cap depending on the breakdown current. The implications of this structure for electric characteristics is analyzed with a spherical thermal-electric model. When ONO films are used as **antifuse** on FPGA product, the resistance of the **antifuse** can be controlled by choosing a sufficiently large programming current level and the resistance remains stable during 1000 h of burn-in at 125 degrees C and 5.75 V. Negligible change in delay time along many different data paths was observed.

Subfile: B

33/3,AB/15 (Item 15 from file: 2)
DIALOG(R)File 2:INSPEC
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04271689 INSPEC Abstract Number: B9212-1265B-093, C9212-5140-001

Title: Actel locate the **antifuse** dielectric

Author(s): Flaherty, N.; Neale, R.

Journal: Electronic Engineering vol.64, no.789 p.41-2, 44, 47

Publication Date: Sept. 1992 Country of Publication: UK

CODEN: ELCEA9 ISSN: 0013-4902

Language: English

Abstract: Actel have recently released the first side elevation TEMs of programmed ONO (oxide-nitride-oxide) **antifuses** of the type used in their family of FPGAs. These new micrographs finally determine the critical post programming location of the dielectric and throw new light on the programming mechanism. The authors explore the new evidence and critically review its interpretation.

Subfile: B C

33/3,AB/16 (Item 16 from file: 2)

DIALOG(R)File 2:INSPEC

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03910659 INSPEC Abstract Number: B91043851, C91041202

Title: A reflow model for the **anti-fuse**

Author(s): Neale, R.

Journal: Electronic Engineering vol.63, no.772 p.31-2, 35-6, 38, 40

Publication Date: April 1991 Country of Publication: UK

CODEN: ELCEA9 ISSN: 0013-4902

Language: English

Abstract: From an investigation that started in response to questions regarding the safety of some of the reliability conclusions drawn with respect to the **anti-fuse** element used in PLDS the author proposes a new and elegant model for the operation of the device, that if fully verified will clear any reliability doubts. A number of different material compositions are used by different manufacturers. They all have the basic metal-thin film dielectric-metal sandwich structure. The dielectric is usually silica ($\text{SiO}_{\text{sub} 2}$) or a layered silica-silicon nitride -silica sandwich composite, other dielectrics such as amorphous silicon are also used. Here devices with dielectrics of a thickness of the order of 100 Å are considered. In operation the application of a voltage of the order 10-20 V results in dielectric breakdown and the establishment of a permanent conducting link with a resistance of from 300 to 1000 Ω . It is that link that is then used to selectively couple the logic elements of the circuit.

Subfile: B C

33/3,AB/17 (Item 17 from file: 2)

DIALOG(R)File 2:INSPEC

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03809770 INSPEC Abstract Number: B91008213

Title: Oxide-nitride-oxide **antifuse** reliability

Author(s): Chiang, S.; Wang, R.; Chen, J.; Hayes, K.; McCollum, J.; Hamdy, E.; Hu, C.

Author Affiliation: Actel Corp., Sunnyvale, CA, USA

Conference Title: 28th Annual Proceedings. Reliability Physics 1990 (Cat.

No. 90CH2787-0) p.186-92

Publisher: IEEE, New York, NY, USA

Publication Date: 1990 Country of Publication: USA vi+322 pp.

U.S. Copyright Clearance Center Code: CH2787-0/90/0000-0186\$01.00

Conference Sponsor: IEEE

Conference Date: 27-29 March 1990 Conference Location: New Orleans, LA, USA

Language: English

Abstract: Compact, low-resistance oxide-nitride-oxide (ONO) **antifuses** are studied for time-dependent dielectric breakdown (TDDB), program disturb, programmed **antifuse** resistance stability, and effective screen. ONO **antifuses** are superior to oxide **antifuses**. No ONO **antifuse** failures were observed in 1.8 million accelerated burn-in device-hours accumulated on 1108 product units. This is in agreement with the 1/E field acceleration model.

Subfile: B

33/3,AB/18 (Item 1 from file: 8)

DIALOG(R)File 8: Ei Compendex(R)

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05792125

E.I. No: EIP01025548923

Title: Scalability study of laser-induced vertical make-link structure

Author: Lee, Joo-Han; Zhang, Wei; Bernstein, Joseph B.

Corporate Source: Univ of Maryland at College Park, College Park, MD, USA

Source: IEEE Transactions on Semiconductor Manufacturing v 13 n 4 Nov 2000. p 442-447

Publication Year: 2000

CODEN: ITSMED ISSN: 0894-6507

Language: English

Abstract: The scalability of a direct metal-to-metal connection between two different levels of metallizations has been extrapolated to be compatible with modern semiconductor fabrication technology. A simple equation to evaluate the scalability was formulated based on focused ion beam (FIB) cross-sectional images of larger link structures with various sizes. With a 0.6- μ m-thick metal 1 line and a 0.5- μ m-thick interlevel dielectric (ILD), a width of less than 0.5 μ m is evaluated to be possible for the metal 1 line. Two limitations exist in the process of scaled-down link structures, which are the ratio of the thickness of ILD to the thickness of the metal 1 line, t_{ILD}/t_{Metal1} , and the quality of laser beam parameters including the spot size and positioning error. However, modern processing technologies and advanced laser processing systems are considered to allow the scalability of a vertical make-link structure. Two layouts of two-level interconnects were designed with increased interconnect densities with a 1- μ m pitch of a 0.5- μ m-wide metal 1 line. These results demonstrate the application of commercially viable vertical linking technology to very large-scale integration (VLSI) applications. (Author abstract) 13 Refs.

33/3,AB/19 (Item 2 from file: 8)

DIALOG(R)File 8: Ei Compendex(R)

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05265460

E.I. No: EIP99034606637

Title: Metal-to-metal **antifuse** with amorphous Ti-rich barium

titanate film and silicon oxide film

Author: Lee, Jae Sung; Lee, Young Hyun

Corporate Source: Uiduk Univ, Kyongbuk-do, South Korea

Source: Solid-State Electronics:An International Journal v 43 n 3 Mar 1999. p 469-472

Publication Year: 1999

CODEN: SSELA5 ISSN: 0038-1101

Language: English

Abstract: This paper is focused on the fabrication of reliable novel **antifuse**, which could operate at low voltage along with the improvement in off and on-state properties. An **antifuse** composed of Ti-rich barium titanate/**silicon oxide** sandwiched between Al and TiW-silicide has been developed for high reliable field programmable devices. The breakdown voltage of an **antifuse** is properly reduced by using amorphous Ti-rich barium titanate film and leakage current is not significantly increased due to the high quality of **silicon oxide**. Low on-resistance (46 Omega / mu m**2) and low programming voltage (9 V) is demonstrated in these **antifuses** with a 220 angstroms double **insulator layer** while keeping sufficient off-state reliability. A significant capacitance reduction at high operating frequencies is also realized. (Author abstract) 6 Refs.

33/3,AB/20 (Item 3 from file: 8)

DIALOG(R)File 8:EI Compendex(R)

(c) 2002 Engineering Info. Inc. All rts. reserv.

05116709

E.I. No: EIP98094374243

Title: New metal-to-metal **antifuse** with **amorphous carbon**

Author: Liu, S.; Lamp, D.; Gangopadhyay, S.; Sreenivas, G.; Ang, S.S.; Naseem, H.A.

Corporate Source: Texas Tech Univ, Lubbock, TX, USA

Source: IEEE Electron Device Letters v 19 n 9 Sep 1998. p 317-319

Publication Year: 1998

CODEN: EDLEDZ ISSN: 0741-3106

Language: English

Abstract: We report the development of a new metal-to-metal **antifuse** with **amorphous carbon** as the dielectric.

Amorphous carbon antifuses have several characteristics making them superior to **amorphous silicon antifuses**, including lower values of OFF-state leakage current, ON-state resistance, dielectric constant, and breakdown voltage. Most importantly, **amorphous carbon antifuses** do not show ON-OFF switching, which is observed in **amorphous silicon antifuses**. A new model is proposed to explain the breakdown mechanism and ON-state reliability of **amorphous carbon antifuses**. (Author abstract) 22 Refs.

33/3,AB/21 (Item 4 from file: 8)

DIALOG(R)File 8:EI Compendex(R)

(c) 2002 Engineering Info. Inc. All rts. reserv.

04616394

E.I. No: EIP97023518606

Title: Investigation of link formation in a novel planar-type **antifuse structure**

Author: Baek, Jong Tae; Park, Hyung-Ho; Kang, Sang Won; Ahn, Byung Tae; Yoo, Ilyung Joun
 Corporate Source: Electronics and Telecommunications Research Inst, Taejon, South Korea

Source: Thin Solid Films v 288 n 1-2 Nov 15 1996. p 41-44
 Publication Year: 1996

CODEN: THSFAP

Language: English

Abstract: A novel **antifuse** structure with planar-type polysilicon pad is described. The formation of a link between the aluminum electrodes after application of a programming voltage was also investigated. The structure consists of Al/SiO₂/poly-Si/SiO₂/Al layers. The poly-Si pad was doped with boron and the thickness of the **antifuse** dielectric was 9 nm. When a programming voltage is applied, the electrodes are connected by the mass transfer of aluminum through the dielectric and the doped polysilicon pad. The on-state resistance of about 10 Omega, which is the lowest on-state resistance ever reported, is obtained after breakdown with 9.9 V programming voltage. Scanning Auger microscopy analyses show the propagation of a link, as mass transfer of aluminum in the boron doped polysilicon pad. The elliptical link has a maximum diameter of 1.0 mu m in the horizontal direction and a minimum diameter of 320 nm in the vertical direction. (Author abstract) 6 Refs.

33/3,AB/22 (Item 5 from file: 8)
 DIALOG(R)File 8:EI Compendex(R)
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04239896

E.I. No: EIP95092839957

Title: **Anti-fuse** developments - a pattern emerges

Author: Anon

Source: Electronic Engineering (London) v 67 n 822 Jun 1995. 3pp

Publication Year: 1995

CODEN: ELEGAP ISSN: 0013-4902

Language: English

Abstract: The IRPS-95 (International Reliability Physics Symposium) has added some more information to the developments of the **amorphous silicon-based anti-fuse**, the M-aSi-M type. The first is the agreed advantage of the low temperature (about 300 degree C) CVD deposition process for **amorphous silicon** as the material most suited for devices that must be deposited late in the process. The second is the confirmation that the effect of voltage stress saturate at a value that would not compromise the off-state integrity when devices are operated at 5V, the normal operating voltage. As the silicon industry in general moves to 3.3V and lower, use of the **amorphous silicon-based anti-fuses** is found to be highly plausible. 6 Refs.

33/3,AB/23 (Item 6 from file: 8)
 DIALOG(R)File 8:EI Compendex(R)
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04229455

E.I. No: EIP95082825068

Title: Electro-thermal model for metal-oxide-metal **antifuses**

Author: Zhang, Guobiao; Hu, Chenming; Yu, Peter Y.; Chiang, Steve; Eltoukhy, Shafy; Hamdy, Esmat Z.

Corporate Source: Univ of California, Berkeley, CA, USA
Source: IEEE Transactions on Electron Devices v 42 n 8 Aug 1995. p
1548-1558

Publication Year: 1995
CODEN: IETDAI ISSN: 0018-9383
Language: English

Abstract: In this paper, a complete electro-thermal analysis is presented for the metal-oxide-metal **antifuses**. The application of the Wiedemann-Franz Law and the thin film effect on thermal and electrical conductivities of metal films were also discussed. Several key parameters for **tungsten-oxide-tungsten** antifuse were extracted. The reaction temperature between **tungsten** and oxide was estimated to be around 1300 degree C. The core resistivity was found to be around 250 μ Omega center dot cm. This model can be readily extended to the other metal-dielectric-metal systems. (Author abstract) 24 Refs.

33/3,AB/24 (Item 7 from file: 8)
DIALOG(R)File 8:EI Compendex(R)
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04209901

E.I. No: EIP95072775471
Title: ON-state, programming and OFF-state reliability of metal-to-metal **antifuse** based 10 nm-thick SiNx film for 3.3 V operation

Author: Tamura, Yoshimitsu; Shinriki, Hiroshi
Corporate Source: Kawasaki Steel Corp, Chiba, Jpn
Conference Title: Proceedings of the 33rd Annual 1995 IEEE International Reliability Physics Proceedings

Conference Location: Las Vegas, NV, USA Conference Date:
19950404-19950406

E.I. Conference No.: 43296
Source: Annual Proceedings - Reliability Physics (Symposium) 1995. IEEE, Piscataway, NJ, USA, 95CH3471-0. p 36-41

Publication Year: 1995
CODEN: ARLPBI ISSN: 0099-9512
Language: English

Abstract: Reliability of newly a developed metal-to-metal **Antifuse** (Al-0.5%Cu/10 nm-thick SiNx/amorphous-like WSix) with very low ON-resistance below 10 ohm has been investigated. Sufficient OFF-state reliability can be obtained by using amorphous-like WSix film as a lower electrode, which has a remarkably smooth surface without sharp protrusions. By using Al-Cu film as an upper electrode, low ON-resistance can be easily obtained with a wide range of programming current down to 0.1 mA, which is enough to melt the lower portion of Al-Cu film and to diffuse aluminum into the SiNx film due to joule heating generated at filament. Moreover, favorable electromigration (EM) performance and ON-state stability of the **Antifuse** programmed in plus polarity could be obtained. The result could be attributed to the final state of the filament composed of Al-W-Si, which is formed by a reaction between electromigrated **tungsten** through ruptured SiNx film and locally melted aluminum just on the ruptured SiNx film due to joule heating. (Author abstract) 10 Refs.

33/3,AB/25 (Item 8 from file: 8)
DIALOG(R)File 8:EI Compendex(R)
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04168604

E.I. No: EIP95052707313

Title: Most promising metal-to-metal **antifuse** based 10 nm-thick p-SiNx film for high density and high speed FPGA application

Author: Tamura, Yoshimitsu; Shinriki, Hiroshi

Corporate Source: Kawasaki Steel Corp, Chiba, Jpn

Conference Title: Proceedings of the 1994 IEEE International Electron Devices Meeting

Conference Location: San Francisco, CA, USA Conference Date: 19941211-19941214

E.I. Conference No.: 43001

Source: Technical Digest - International Electron Devices Meeting 1994. IEEE, Piscataway, NJ, USA, 94CH35706. p 285-288

Publication Year: 1994

CODEN: TDIMD5 ISSN: 0163-1918

Language: English

Abstract: A novel metal-to-metal **Antifuse** has been developed for highly reliable and high performance 3.3 V operated FPGAs. Dielectric breakdown reliability is remarkably improved by using amorphous-like WSix film as a bottom electrode having extremely smooth surface. Sufficient low ON-resistance (8.2 Omega) and low programming voltage (9 V) can be also obtained in the metal-to-metal **Antifuses** having WSix/SiNx(10 nm)/TiN structure while keeping sufficient OFF-state reliability. By using WSix/SiNx/Al-Cu structure, lowest ON-resistance (2 omega) can be obtained. These metal-to-metal **Antifuse** structures are very promising for next generation FPGAs. (Author abstract) 5 Refs.

33/3,AB/26 (Item 9 from file: 8)

DIALOG(R)File 8: Ei Compendex(R)

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03907150

E.I. No: EIP94061318350

Title: Highly reliable metal-to-metal **antifuse** for high-speed field programmable gate arrays

Author: Takagi, Mariko; Yoshii, Ichiro; Ikeda, Naoki; Yasuda, Hiroaki; Hama, Kaoru

Corporate Source: Toshiba Corp, Kawasaki, Jpn

Conference Title: Proceedings of the 1993 IEEE International Electron Devices Meeting

Conference Location: Washington, DC, USA Conference Date: 19931205-19931208

E.I. Conference No.: 20137

Source: Technical Digest - International Electron Devices Meeting 1993. Publ by IEEE, IEEE Service Center, Piscataway, NJ, USA. p 31-34

Publication Year: 1993

CODEN: TDIMD5 ISSN: 0163-1918 ISBN: 0-7803-1450-6

Language: English

Abstract: This paper describes a novel metal-to-metal **antifuse** technology for field programmable gate arrays which achieves very high performance and reliability while maintaining full CMOS compatibility. Plasma-CVD SiN with Si-N equals 1 and Al covered with TiN are used as an **antifuse** dielectric and electrodes, respectively. This structure allows a desirable characteristics for high-speed FPGAs with off-state reliability of 1.7 multiplied by 10**5 years. (Author abstract) 5 Refs.

33/3,AB/27 (Item 10 from file: 8)
DIALOG(R)File 8:EI Compendex(R)
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03409511

E.I. Monthly No: EI9204049261
Title: A sublithographic **antifuse** structure for field-programmable gate array applications.
Author: Chen, Kueing-Long; Liu, David K. Y.; Misium, George; Gosney, W. Milton; Wang, Shoue-Jen; Camp, Janet; Tigelaar, Howard
Corporate Source: Texas Instruments Inc, Dallas, TX, USA
Source: IEEE Electron Device Letters v 13 n 1 Jan 1992 p 53-55
Publication Year: 1992
CODEN: EDLEDZ ISSN: 0193-8576
Language: English

Abstract: The authors demonstrate an **antifuse** structure with a cell area of 0.2 multiplied by $0.2 \mu m^{**2}$ which is fabricated by using the vertical sidewall of a polysilicon interconnect layer and two-mask patterning and etching steps. The **antifuse** is constructed in such a way that its vertical dimension is determined by the thickness of the polysilicon layer, and its horizontal dimension is determined by two-mask patterning and etching steps. For a conventional contact-hole type of structure, a $0.2- \mu m$ lithographic capability will be required to achieve the same **antifuse** cell size. It is also demonstrated that the time-dependent dielectric breakdown (TDDB) reliability of this sidewall **antifuse** is as good as that of a conventional planar contact-hole **antifuse**. 3 Refs.

33/3,AB/28 (Item 1 from file: 34)
DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2002 Inst for Sci Info. All rts. reserv.

05497422 Genuine Article#: WC476 Number of References: 8
Title: 2-DIMENSIONAL MODELING FOR THE CURRENT-DENSITY DISTRIBUTION IN A HEAVILY-DOPED SEMICONDUCTOR RESISTOR (Abstract Available)
Author(s): KIM JD; KOO JG; NAM KS
Corporate Source: ELECT & TELECOMMUN RES INST, SEMICOND DIV, POB 106/TAEJON 305600//SOUTH KOREA/
Journal: INTERNATIONAL JOURNAL OF ELECTRONICS, 1997, V82, N1 (JAN), P19-25
ISSN: 0020-7217
Language: ENGLISH Document Type: ARTICLE
Abstract: A two-dimensional model for the calculation of the current density distribution in a heavily doped semiconductor resistor is described as a function of time and position along the width and length. During the initial stages of the discharge, when the total current is increasing rapidly with time, the current first appears at the **edges** of the resistor. After the initial stages, the current diffuses from the **edges** toward the centre of the device. The new model described in this paper may aid in explaining the behaviours of uneven melting and programming of semiconductor bridges and **antifuse** devices, respectively.

33/3,AB/29 (Item 2 from file: 34)
DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
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05032516 Genuine Article#: TK562 Number of References: 7

Title: INTERFACIAL REACTION IN THE SPUTTER-DEPOSITED $\text{SiO}_2/\text{TiO}_{0.1}\text{W}_{0.9}$

ANTIFUSE SYSTEM (Abstract Available)

Author(s): BAEK JT; PARK HH; CHO KI; YOO HJ; KANG SW; AHN BT

Corporate Source: ELECTR & TELECOMMUN RES INST, DIV SEMICOND TECHNOL, YUSONG
PO BOX 106/TAEJON 305600//SOUTH KOREA/

Journal: JOURNAL OF APPLIED PHYSICS, 1995, V78, N12 (DEC 15), P7074-7079

ISSN: 0021-8979

Language: ENGLISH Document Type: ARTICLE

Abstract: The effects of annealing temperature on the interfacial reactions and the antifuse I-V characteristics of ultra thin SiO_2 layer deposited on $\text{TiO}_{0.1}\text{W}_{0.9}$ substrate were investigated. The interfacial reactions were analyzed using x-ray photoelectron spectroscopy and Auger electron spectroscopy with the sample which is in situ annealed under ultra high vacuum or ex situ annealed in a nitrogen atmosphere. The surface of the $\text{TiO}_{0.1}\text{W}_{0.9}$ substrate was oxidized during sputter deposition of SiO_2 layer. Ti, W oxides consist of Ti_{2}O_3 (Ti_{3}O_5), TiO_2 , W_2O_3 , and WO_3 . The WO_3 and Ti_{2}O_3 decomposed into metallic W and Ti at 400 and 500 degrees C, respectively. The breakdown voltage of the antifuse decreased as the annealing temperature increased, due to the thinning of dielectric layer resulted from the decomposition of Ti, W oxides and the formation of metallic W and Ti. Annealing at 600 degrees C caused the reaction between metallic (Ti,W) and SiO_2 layer and formed elemental silicon in the dielectric layer, where SiO_2 layer completely lost its dielectric property. The breakdown of dielectric property might form a metallic channel in the SiO_2 film, which mainly contains metallic W, Ti, and Si. (C) 1995 American Institute of Physics.

33/3,AB/30 (Item 3 from file: 34)

DIALOG(R)File 34:SciSearch(R) Cited Ref Sci

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04736478 Genuine Article#: UD941 Number of References: 7

Title: EXTREMELY LOW ON-RESISTANCE METAL-TO-METAL ANTIFUSES WITH AL-CU/10-NM THICK P-SINX/AL-CU STRUCTURE FOR NEXT-GENERATION VERY-HIGH-SPEED FPGAS (FIELD-PROGRAMMABLE GATE ARRAYS)

(Abstract Available)

Author(s): TAMURA Y; KIMURA Y; TSUTSUI C; SHINRIKI H

Corporate Source: KAWASAKI STEEL CHEM IND CO LTD, ADV TECHNOL RES SECT, LARGE SCALE INTEGRAT DIV, CHUOH KU/CHIBA 260//JAPAN/

Journal: JAPANESE JOURNAL OF APPLIED PHYSICS PART 1-REGULAR PAPERS SHORT NOTES & REVIEW PAPERS, 1996, V35, N2B (FEB), P1049-1053

ISSN: 0021-4922

Language: ENGLISH Document Type: ARTICLE

Abstract: We present a novel, metal-to-metal antifuse structure consisting of a plasma enhanced CVD (chemical vapor deposition) silicon nitride (p-SiNx) dielectric film sandwiched between two aluminum layers. The leakage current in the off-state is markedly reduced by using aluminum film as the upper electrode instead of Ti (titanium) or TiN (titanium nitride) film. A Al-Cu/10 nm-thick p-SiNx/Al-Cu structure antifuse provides sufficient long-term off-state reliability exceeding ten years at 3.6 V while keeping low breakdown voltage (10 V). An extremely low on-resistance of around 3 Omega and a narrow distribution are also realized. A new antifuse structure (Al-Cu/p-SiNx/Al-Cu(100 nm)/Ti/TiN/Al-Cu) highly compatible with the conventional via formation

process in double metal interconnect wiring is proposed. This type of antifuse structure is very promising for next-generation very high-speed FPGAs.

33/3,AB/31 (Item 1 from file: 35)
DIALOG(R)File 35:Dissertation Abs Online
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01562770 AAD9718496
DEPOSITION, CHARACTERIZATION, AND DEVICE APPLICATION OF AMORPHOUS CARBON AND AMORPHOUS SILICON FILMS (ANTIFUSES)

Author: LIU, SHIXI

Degree: PH.D.

Year: 1987

Corporate Source/Institution: TEXAS TECH UNIVERSITY (0230)

Source: VOLUME 58/01-B OF DISSERTATION ABSTRACTS INTERNATIONAL.

PAGE 250. 221 PAGES

The purpose of this work is to develop an expertise of deposition of amorphous carbon (a-C) films, especially diamond-like carbon (DLC) films using various deposition systems, and to acquire better understandings of this material by various characterization techniques, and finally to study the feasibility of using this material as a new dielectric for Metal-to-Metal antifuse devices to solve the switching problem of the amorphous silicon (a-Si) antifuses.

In this work, we report successful deposition of DLC films using a microwave electron cyclotron resonance (ECR) plasma system. We found that a-C:H films deposited without rf biasing are soft and polymer-like and have higher band gaps. DLC films can only be produced under a negative self-bias induced by the rf biasing. The band gap of the film decreases with the increase in rf power, and with the decrease in deposition pressure. This shows that the properties of the films depend mainly on the ion bombardment energy.

For a more in-depth investigation of amorphous carbon, a-C:H and its alloys (a-C:H,N,F) deposited using an rf plasma enhanced chemical vapor deposition (PECVD) system at the University of Arkansas were used. We have used infrared (IR), optical absorption, and continuous (cw) and time resolved photoluminescence (PL) to characterize these materials. We have calculated the normal mode vibrational frequencies of nitrogen and fluorine related modes using simple valence force field method. We also studied the effects of nitrogen and fluorine on the film's properties. Our optical absorption and PL data support the cluster model proposed by Robertson that a-C:H contains both sp\$\\sp2\$ and sp\$\\sp3\$ sites, with sp\$\\sp2\$ clusters embedded in sp\$\\sp3\$ bonded matrix.

For this work, a-C:H and its alloys (a-C:H,N,F) were employed as potential dielectrics for the Metal-to-Metal antifuse development. We found that these new antifuses have several characteristics superior to a-Si antifuses including lower values of OFF-state leakage current, ON-state resistance, dielectric constant and breakdown voltage. Most importantly, these new antifuses do not show ON-OFF switching which is observed in a-Si antifuses. Finally a phase transition model is proposed to explain the breakdown mechanism and ON-state reliability in amorphous carbon antifuses.

33/3,AB/32 (Item 1 from file: 94)
DIALOG(R)File 94:JICST-EPlus

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03647050 JICST ACCESSION NUMBER: 98A0682562 FILE SEGMENT: JICST-E
The Synergistic Inhibition Effects of Hard Base and Oxidizing Inhibitors on
Pit Initiation and Growth of a Passive Film on Iron.
ARAMAKI KUNITSUGU (1); FUJIOKA EIJI (1)
(1) Keio Univ., Fac. of Sci. and Technol.
Zairyo to Kankyo(Corrosion Engineering), 1998, VOL.47,NO.7, PAGE.460-467,
FIG.9, TBL.2, REF.18
JOURNAL NUMBER: F0006ABY ISSN NO: 0917-0480
UNIVERSAL DECIMAL CLASSIFICATION: 669:620.197
LANGUAGE: Japanese COUNTRY OF PUBLICATION: Japan
DOCUMENT TYPE: Journal
ARTICLE TYPE: Original paper
MEDIA TYPE: Printed Publication
ABSTRACT: The synergistic inhibition effects of a hard base,
octylthiopropionate ion $C_8H_{17}S(CH_2)_2-COO^-$ (OTP-) and various
oxidizing inhibitors on pit nucleation and growth were investigated for
a passivated iron electrode in an aerated borate buffer solution
(pH8.49) containing an aggressive anion Cl^- by polarization
measurements. Because the pitting potential E_{pit} and the repassivation
potential E_{rep} were mostly shifted in the positive direction by
mixtures of OTP- plus MoO_4^{2-} , WO_4^{2-} , NO_3^- , and NO_2^- , these
inhibitor mixtures suppressed both pit nucleation and growth. Mixtures
of OTP- plus CrO_4^{2-} and VO_3^- inhibited pit initiation but
stimulated pit propagation, resulting in the formation of large pits.
The hard bases, OTP- and oxidizing inibitors suppressed pit
nucleation by repairing defects in the passive film with deposits of
their salts or complexes. After pit initiation, since oxidizing
inhibitors like WO_4^{2-} and NO_3^- oxidized the iron substrate surface at
the bottom of a pit to change a soft acid to a hard one, they inhibited
pit growth by precipitation of oxides within the pit. Inhibition of pit
nucleation and growth on the passive iron surface was closely related
to the hard and soft acids and bases(HSAB) principle. (author abst.)

33/3,AB/33 (Item 2 from file: 94)
DIALOG(R)File 94:JICST-EPlus
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03189800 JICST ACCESSION NUMBER: 97A0332765 FILE SEGMENT: JICST-E
Hardening of anodic oxidation coating of aluminium in barium hydroxide
alkaline bath with addition of ion of oxygen acid.
OKUMURA KATSUTARO (1); FUJINO TAKAYOSHI (1); NOGUCHI HAYAO (1)
(1) Kinki Univ., Fac. of Sci. and Technol.
Aruminiuumu Kenkyu Kaishi(Journal of the Japanese Anodizing Association),
1997, NO.2, PAGE.83-84, FIG.1, TBL.1, REF.3
JOURNAL NUMBER: F0591ABP ISSN NO: 0285-5224
UNIVERSAL DECIMAL CLASSIFICATION: 621.794
LANGUAGE: Japanese COUNTRY OF PUBLICATION: Japan
DOCUMENT TYPE: Journal
ARTICLE TYPE: Short Communication
MEDIA TYPE: Printed Publication
ABSTRACT: The anodizing was carried out in the mixed bath of $Ba(OH)_2$ and
oxoate such as sodium aluminate (SA), sodium tetraborate (S4B), and
titanium potassium oxalate (OTP) to investigate their effect on
the hardness of anodized film. The anodized film made from the bath of
SA and OTP was not hard, while those from the bath of S4B and
 $Ba(OH)_2$ were hard. Pores of diameter of 500A were observed in the

above-said four kinds of film. The hard film was made of dense cell structure.

33/3,AB/34 (Item 1 from file: 144)
 DIALOG(R)File 144:Pascal
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13040518 PASCAL No.: 97-0327083
 A new low-resistance **antifuse** with planar metal/dielectric/poly-Si/dielectric/metal structure
 Solid state devices and materials
 BAEK J T; CHUNG S H; KANG S W; AHN B T; YOO H J
 ARAKAWA Yasuhiro, ed; ARIMOTO Yoshihiro, ed; HATTORI Takeo, ed; HIRAYAMA Yoshiro, ed; ISHIBASHI Akira, ed; KASAHARA Kenichi, ed; KONAGAI Makoto, ed; KOYANAGI Mitsumasa, ed; MATSUMOTO Kazuhiko, ed; MIYAZAKI Seiichi, ed; NATORI Kenji, ed; ONABE Kentaro, ed; SHIBATA Tadashi, ed; SUEMUNE Ikuo, ed; TABE Michiharu, ed; TSUBOUCHI Kazuo, ed; YOKOYAMA Naoki, ed; YOSHIMI Makoto, ed

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Japan Society of Applied Physics, Tokyo, Japan.
 1996 International Conference on Solid State Devices and Materials (SSDM'96) (Yokohama JPN) 1996-08-26

Journal: Japanese journal of applied physics, 1997, 36 (3B p.1)
 1642-1645

Language: English
 A new **antifuse** with metal/dielectric/poly-Si/dielectric/metal structure has been developed for use in FPGAs as a voltage programmable link. This structure has two thermally grown dielectrics with an 8.5nm thickness and a boron-doped poly-Si pad. Low programmed on-state resistance of similar 20 OMEGA was achieved by the formation of Al-Si metal alloy link in the doped poly-Si pad. The metal link was formed by the diffusion of Al from the positive electrode into poly-Si. The dielectric property of this **antifuse** might be reliable because of no hillocks on the bottom electrode and no interaction between the thermally grown SiO SUB 2 and the bottom electrode.

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33/3,AB/35 (Item 2 from file: 144)
 DIALOG(R)File 144:Pascal
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12555534 PASCAL No.: 96-0236139
 Extremely low ON-resistance metal-to-metal **antifuses** with Al-Cu/10 nm-thick p-SiN SUB x /Al-Cu structure for next generation very high speed FPGAs : Field programmable gate arrays)

Solid state devices and materials
 TAMURA Y; KIMURA Y; TSUTSUI C; SHINRIKI H
 ARAKAWA Yasuhiro, ed; FUKUI Takashi, ed; FUKUMA Masao, ed; FURUYA Kazuhito, ed; ISHIWARA Hiroshi, ed; MATSUMOTO Kazuhiko, ed; MATSUMURA Masakiyo, ed; TABE Michiharu, ed; TANIGUCHI Kenji, ed; TARUCHA Seigo, ed; TSUBOUCHI Kazuo, ed; YOKOYAMA Naoki, ed
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 Minato-ku, Tokyo 106, Japan

Japan Society of Applied Physics, Tokyo, Japan.
 SSDM'95. International Conference (Osaka JPN) 1995-08-21
 Journal: Japanese journal of applied physics, 1996, 35 (2B p.1)
 1049-1053

Language: English
 We present a novel metal-to-metal **antifuse** structure consisting of a plasma enhanced CVD (chemical vapor deposition) silicon nitride (p-SiN SUB x) dielectric film sandwiched between two aluminum layers. The leakage current in the off-state is markedly reduced by using aluminum film as the upper electrode instead of Ti (titanium) or TiN (titanium nitride) film. A Al-Cu/10 nm-thick p-SiN SUB x /Al-Cu structure antifuse provides sufficient long-term off-state reliability exceeding ten years at 3.6 V while keeping low breakdown voltage (10 V). An extremely low on-resistance of around 3 OMEGA and a narrow distribution are also realized. A new antifuse structure (Al-Cu/p-SiN SUB x /Al-Cu(100 nm)/Ti/TiN/Al-Cu) highly compatible with the conventional via formation process in double metal interconnect wiring is proposed. This type of antifuse structure is very promising for next-generation very high-speed FPGAs.

33/3,AB/36 (Item 3 from file: 144)
 DIALOG(R)File 144:Pascal
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12341571 PASCAL No.: 95-0582776
 Interfacial reaction in the sputter-deposited SiO SUB 2 /Ti SUB 0
 SUB . SUB 1 W SUB 0 SUB . SUB 9 **antifuse** system
 BAEK Jong Tae; PARK Hyung-Ho; CHO Kyung-Ik; YOO Hyung Joun; KANG Sang Won
 ; AHN Byung Tae
 Semiconductor Technology Division, Electronics and Telecommunications
 Research Institute, Yusong P.O. Box 106, Taejon 305-600, Korea
 Journal: Journal of Applied Physics, 1995-12-15, 78 (12) 7074-7079
 Language: English
 The effects of annealing temperature on the interfacial reactions and the antifuse I-V characteristics of ultra thin SiO SUB 2 layer deposited on Ti SUB 0 SUB . SUB 1 W SUB 0 SUB . SUB 9 substrate were investigated. The interfacial reactions were analyzed using x-ray photoelectron spectroscopy and Auger electron spectroscopy with the sample which is in situ annealed under ultra high vacuum or ex situ annealed in a nitrogen atmosphere. The surface of the Ti SUB 0 SUB . SUB 1 W SUB 0 SUB . SUB 9 substrate was oxidized during sputter deposition of SiO SUB 2 layer. Ti, W oxides consist of Ti SUB 2 O SUB 3 (Ti SUB 3 O SUB 5), TiO SUB 2 , WO SUB 2 , and WO SUB 3 . The WO SUB 3 and Ti SUB 2 O SUB 3 decomposed into metallic W and Ti at 400 and 500 Degree C, respectively. The breakdown voltage of the **antifuse** decreased as the annealing temperature increased, due to the thinning of dielectric layer resulted from the decomposition of Ti, W oxides and the formation of metallic W and Ti. Annealing at 600 Degree C caused the reaction between metallic (Ti,W) and SiO SUB 2 layer and formed elemental silicon in the dielectric layer, where SiO SUB 2 layer completely lost its dielectric property. The breakdown of dielectric property might form a metallic channel in the SiO SUB 2 film, which mainly contains metallic W, Ti, and Si. (c) 1995
 American Institute of Physics.

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33/3,AB/37 (Item 4 from file: 144)
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12076438 PASCAL No.: 95-0278333
Novel **amorphous-silicon-based** double-metal **antifuse**
with barrier enhancement layer
YEAU-KUEN FANG; KUEN-HSIEN LEE; FU-YUAN CHEN; JUN-DAR HWANG
National Cheng Kung univ., dep. electrical eng., VLSI technology lab.,
Tainan, Taiwan

Journal: Japanese journal of applied physics, 1995, 34 (4A p.1)
1736-1740

Language: English

The electrical characteristics, operating mechanism and reliability of a novel **amorphous-silicon-based** double-metal **antifuse** are reported in detail. A very thin alpha -SiC:H layer was inserted on both top and bottom Al/alpha -Si:H interfaces as barrier enhancement layer. With proper adjustment of the thickness of this layer, the programming voltage and leakage current can be controlled. The **antifuse** offers very low on-resistance (<2 OMEGA) and low preparation temperature (<250 SUP o C), and the characteristics are independent of area, therefore, the device is suitable for integration with field-programmable gate array applications

33/3,AB/38 (Item 1 from file: 65)
DIALOG(R)File 65:Inside Conferences
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01311860 INSIDE CONFERENCE ITEM ID: CN012896050
Extremely Low ON-Resistance Metal to Metal **Antifuses** with Al/p-SiN/Al Structure for Next Generation FPGAs

Kimura, Y.; Tamura, Y.; Tsutsui, C.; Shinriki, H.
CONFERENCE: Solid state devices and materials-International conference
SOLID STATE DEVICES AND MATERIALS, 1995 P: 377-379

The Society, 1995

ISSN: NONE-0293 ISBN: 4930813646

LANGUAGE: English DOCUMENT TYPE: Conference Selected extended abstracts and programme

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CONFERENCE DATE: Aug 1995 (199508) (199508)

NOTE:

Also known as SSDM'95. Includes papers presented at the symposium on amorphous and crystalline insulating thin films III